GigaDevice Semiconductor Inc.

GD32E103xx ARM® Cortex[™]-M4 32-bit MCU

Datasheet



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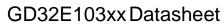




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1. General description

The GD32E103xx device belongs to the connectivity line of GD32 MCU Family. It is a 32-bit general-purpose microcontroller based on the ARM® Cortex™-M4 RISC core with best cost-performance ratio in terms of enhanced processing capacity, reduced power consumption and peripheral set. The Cortex™-M4 core features implements a full set of DSP instructions to address digital signal control markets that demand an efficient, easy-to-use blend of control and signal processing capabilities. It also provides powerful trace technology for enhanced application security and advanced debug support.

The GD32E103xx device incorporates the ARM® Cortex®-M4 32-bit processor core operating at 120 MHz frequency with Flash accesses zero wait states to obtain maximum efficiency. It provides up to 128 KB on-chip Flash memory and 32 KB SRAM memory. An extensive range of enhanced I/Os and peripherals connected to two APB buses. The devices offer up to two 12-bit 3 MSPS ADCs, two 12-bit DACs, up to ten general 16-bit timers, two 16-bit PWM advanced timers, and two 16-bit basic timers, as well as standard and advanced communication interfaces: up to three SPIs, two I2Cs, three USARTs and two UARTs, two I2Ss, an USBFS and two CANs.

The device operates from 1.71 to 3.6 V power supply and available in -40 to +85 °C temperature range. Several power saving modes provide the flexibility for maximum optimization between wakeup latency and power consumption, an especially important consideration in low power applications.

The above features make GD32E103xx devices suitable for a wide range of interconnection and advanced applications, especially in areas such as industrial control, motor drives, consumer and handheld equipment, human machine interface, security and alarm systems, POS, automotive navigation, IoT and so on.





2. Device overview

2.1. Device information

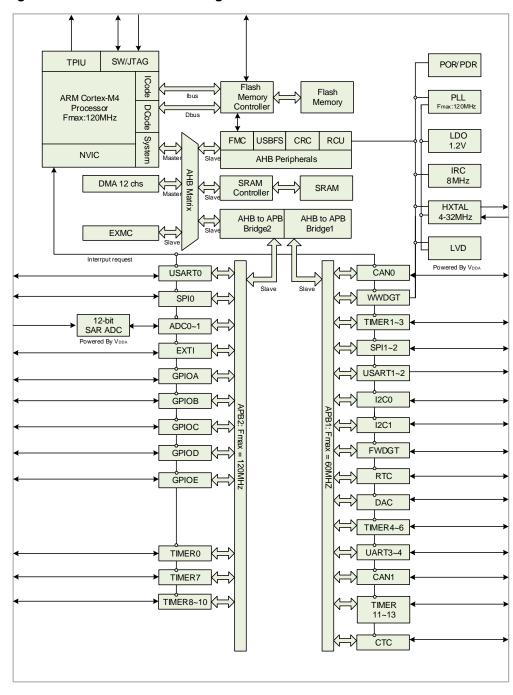
Table 2-1. GD32E103xx devices features and peripheral list

					GD32	E103xx			
	Part Number		тв	C8	СВ	R8	RB	V8	VB
Flash (KB)		64	128	64	128	64	128	64	128
	SRAM (KB)	20	32	20	32	20	32	20	32
	General timer(16-	4	4	10	10	10	10	10	10
	bit)	(1-4)	(1-4)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)
	Advanced	1	1	1	1	2	2	2	2
	timer(16-bit)	(0)	(0)	(0)	(0)	(0,7)	(0,7)	(0,7)	(0,7)
Timers	SysTick	1	1	1	1	1	1	1	1
į	Basic timer(16-bit)	2	2	2	2	2	2	2	2
	Basic timer (10-bit)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)
	Watchdog	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1
	USART	2	2	3	3	3	3	3	3
	USARI	(0-1)	(0-1)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)
	UART	0	0	0	0	2	2	2	2
-⊊	9 7					(3-4)	(3-4)	(3-4)	(3-4)
Connectivity	I2C	1	1	2	2	2	2	2	2
nne		(0)	(0)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)
ပိ	SPI/I2S	1/0	1/0	3/2	3/2	3/2	3/2	3/2	3/2
		(0/-)	(0/-)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)
	CAN	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD
	USBFS	1	1	1	1	1	1	1	1
	GPIO	26	26	37	37	51	51	80	80
	EXMC		0	0	0	0	0	1	1
	EXTI		16	16	16	16	16	16	16
ي	Units	2	2	2	2	2	2	2	2
ADC	Channels	10	10	10	10	16	16	16	16
	DAC		2	2	2	2	2	2	2
	Package	QFI	V36	LQF	- -P48	LQF	P64	LQFF	P100



2.2. Block diagram

Figure 2-1.GD32E103xx block diagram





2.3. Pinouts and pin assignment

Figure 2-2. GD32E103Vx LQFP100 pinouts

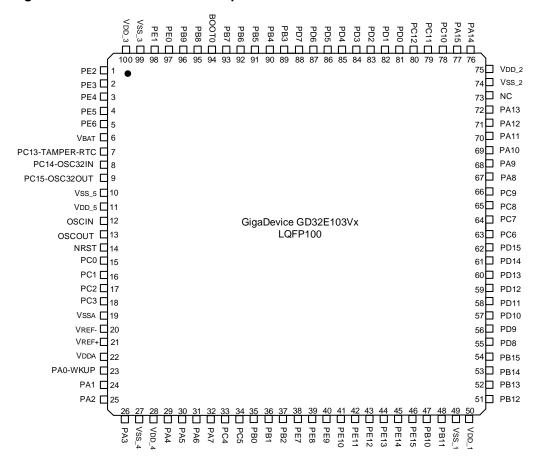




Figure 2-3. GD32E103Rx LQFP64 pinouts

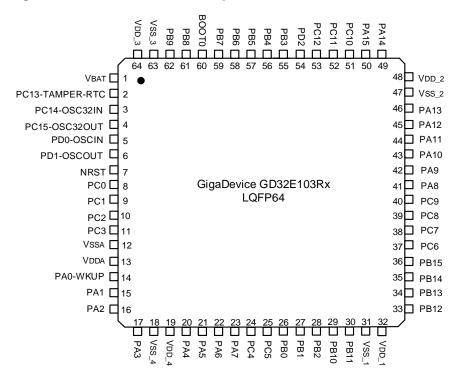


Figure 2-4. GD32E103Cx LQFP48 pinouts

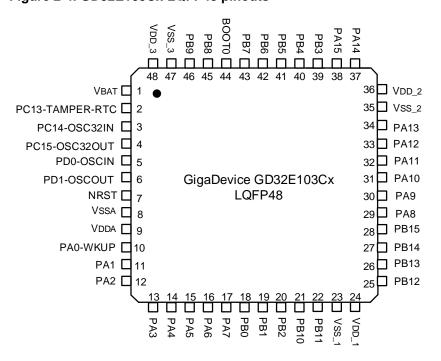
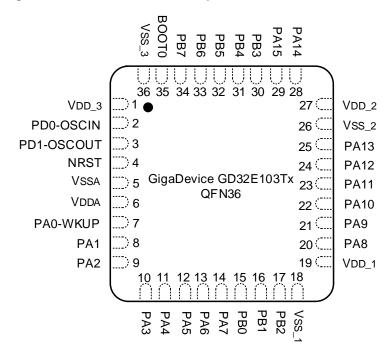




Figure 2-5. GD32E103Tx QFN36 pinouts



2.4. Memory map

Table 2-2. GD32E103xx memory map

Pre-defined regions	Bus	Address	Peripherals
External device		0xA000 0000 - 0xA000 0FFF	EXMC - SWREG
		0x9000 0000 - 0x9FFF FFFF	Reserved
External RAM	AHB3	0x7000 0000 - 0x8FFF FFFF	Reserved
External NAIVI		0,6000,0000,0,6355,555	EXMC -
		0x6000 0000 - 0x63FF FFFF	NOR/PSRAM/SRAM
		0x5000 0000 - 0x5003 FFFF	USBFS
		0x4008 0000 - 0x4FFF FFFF	Reserved
		0x4004 0000 - 0x4007 FFFF	Reserved
		0x4002 BC00 - 0x4003 FFFF	Reserved
		0x4002 B000 - 0x4002 BBFF	Reserved
		0x4002 A000 - 0x4002 AFFF	Reserved
Peripheral	AHB1	0x4002 8000 - 0x4002 9FFF	Reserved
		0x4002 6800 - 0x4002 7FFF	Reserved
		0x4002 6400 - 0x4002 67FF	Reserved
		0x4002 6000 - 0x4002 63FF	Reserved
		0x4002 5000 - 0x4002 5FFF	Reserved
		0x4002 4000 - 0x4002 4FFF	Reserved
		0x4002 3C00 - 0x4002 3FFF	Reserved





				Datasi icci
Pre-def		Bus	Address	Peripherals
			0x4002 3800 - 0x4002 3BFF	Reserved
			0x4002 3400 - 0x4002 37FF	Reserved
			0x4002 3000 - 0x4002 33FF	CRC
			0x4002 2C00 - 0x4002 2FFF	Reserved
			0x4002 2800 - 0x4002 2BFF	Reserved
			0x4002 2400 - 0x4002 27FF	Reserved
			0x4002 2000 - 0x4002 23FF	FMC
			0x4002 1C00 - 0x4002 1FFF	Reserved
			0x4002 1800 - 0x4002 1BFF	Reserved
			0x4002 1400 - 0x4002 17FF	Reserved
			0x4002 1000 - 0x4002 13FF	RCU
			0x4002 0C00 - 0x4002 0FFF	Reserved
			0x4002 0800 - 0x4002 0BFF	Reserved
			0x4002 0400 - 0x4002 07FF	DMA1
			0x4002 0000 - 0x4002 03FF	DMA0
			0x4001 8400 - 0x4001 FFFF	Reserved
			0x4001 8000 - 0x4001 83FF	Reserved
			0x4001 7C00 - 0x4001 7FFF	Reserved
			0x4001 7800 - 0x4001 7BFF	Reserved
			0x4001 7400 - 0x4001 77FF	Reserved
			0x4001 7000 - 0x4001 73FF	Reserved
			0x4001 6C00 - 0x4001 6FFF	Reserved
			0x4001 6800 - 0x4001 6BFF	Reserved
			0x4001 5C00 - 0x4001 67FF	Reserved
			0x4001 5800 - 0x4001 5BFF	Reserved
			0x4001 5400 - 0x4001 57FF	TIMER10
			0x4001 5000 - 0x4001 53FF	TIMER9
		4.000	0x4001 4C00 - 0x4001 4FFF	TIMER8
		APB2	0x4001 4800 - 0x4001 4BFF	Reserved
			0x4001 4400 - 0x4001 47FF	Reserved
			0x4001 4000 - 0x4001 43FF	Reserved
			0x4001 3C00 - 0x4001 3FFF	Reserved
			0x4001 3800 - 0x4001 3BFF	USART0
			0x4001 3400 - 0x4001 37FF	TIMER7
			0x4001 3000 - 0x4001 33FF	SPI0
			0x4001 2C00 - 0x4001 2FFF	TIMER0
			0x4001 2800 - 0x4001 2BFF	ADC1
			0x4001 2400 - 0x4001 27FF	ADC0
			0x4001 2000 - 0x4001 23FF	Reserved
1			2000 0001 2011	1.000.100





5		32322	USXX DataSHEE
Pre-defined regions	Bus	Address	Peripherals
		0x4001 1C00 - 0x4001 1FFF	Reserved
		0x4001 1800 - 0x4001 1BFF	GPIOE
		0x4001 1400 - 0x4001 17FF	GPIOD
		0x4001 1000 - 0x4001 13FF	GPIOC
		0x4001 0C00 - 0x4001 0FFF	GPIOB
		0x4001 0800 - 0x4001 0BFF	GPIOA
		0x4001 0400 - 0x4001 07FF	EXTI
		0x4001 0000 - 0x4001 03FF	AFIO
		0x4000 CC00 - 0x4000 FFFF	Reserved
		0x4000 C800 - 0x4000 CBFF	СТС
		0x4000 C400 - 0x4000 C7FF	Reserved
		0x4000 C000 - 0x4000 C3FF	Reserved
		0x4000 8000 - 0x4000 BFFF	Reserved
		0x4000 7C00 - 0x4000 7FFF	Reserved
		0x4000 7800 - 0x4000 7BFF	Reserved
		0x4000 7400 - 0x4000 77FF	DAC
		0x4000 7000 - 0x4000 73FF	PMU
		0x4000 6C00 - 0x4000 6FFF	BKP
		0x4000 6800 - 0x4000 6BFF	CAN1
		0x4000 6400 - 0x4000 67FF	CAN0
		0x4000 6000 - 0x4000 63FF	CAN SRAM 1K bytes
		0x4000 5C00 - 0x4000 5FFF	Reserved
		0x4000 5800 - 0x4000 5BFF	I2C1
	APB1	0x4000 5400 - 0x4000 57FF	I2C0
		0x4000 5000 - 0x4000 53FF	UART4
		0x4000 4C00 - 0x4000 4FFF	UART3
		0x4000 4800 - 0x4000 4BFF	USART2
		0x4000 4400 - 0x4000 47FF	USART1
		0x4000 4000 - 0x4000 43FF	Reserved
		0x4000 3C00 - 0x4000 3FFF	SPI2/I2S2
		0x4000 3800 - 0x4000 3BFF	SPI1/I2S1
		0x4000 3400 - 0x4000 37FF	Reserved
		0x4000 3000 - 0x4000 33FF	FWDGT
		0x4000 2C00 - 0x4000 2FFF	WWDGT
		0x4000 2800 - 0x4000 2BFF	RTC
		0x4000 2400 - 0x4000 27FF	Reserved
		0x4000 2000 - 0x4000 23FF	TIMER13
		0x4000 1C00 - 0x4000 1FFF	TIMER12
		0x4000 1800 - 0x4000 1BFF	TIMER11



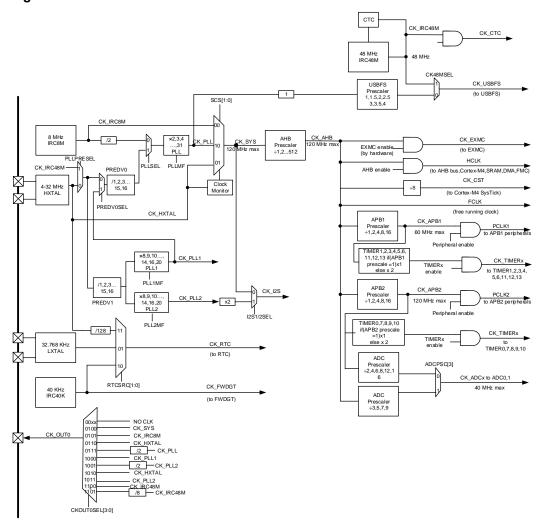
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Dec defined			
Pre-defined regions	Bus	Address	Peripherals
. og.o		0x4000 1400 - 0x4000 17FF	TIMER6
		0x4000 1000 - 0x4000 13FF	TIMER5
		0x4000 0C00 - 0x4000 0FFF	TIMER4
		0x4000 0800 - 0x4000 0BFF	TIMER3
		0x4000 0400 - 0x4000 07FF	TIMER2
		0x4000 0000 - 0x4000 03FF	TIMER1
		0x2007 0000 - 0x3FFF FFFF	Reserved
		0x2006 0000 - 0x2006 FFFF	Reserved
		0x2003 0000 - 0x2005 FFFF	Reserved
		0x2002 0000 - 0x2002 FFFF	Reserved
SRAM	AHB	0x2001 C000 - 0x2001 FFFF	
		0x2001 8000 - 0x2001 BFFF	
		0x2000 5000 - 0x2001 7FFF	SRAM
		0x2000 0000 - 0x2000 4FFF	
		0x1FFF F810 - 0x1FFF FFFF	Reserved
		0x1FFF F800 - 0x1FFF F80F	Option Bytes
		0x1FFF F000 - 0x1FFF F7FF	
		0x1FFF C010 - 0x1FFF EFFF	-
		0x1FFF C000 - 0x1FFF C00F	Boot loader
		0x1FFF B000 - 0x1FFF BFFF	1
		0x1FFF 7A10 - 0x1FFF AFFF	Reserved
		0x1FFF 7800 - 0x1FFF 7A0F	Reserved
		0x1FFF 0000 - 0x1FFF 77FF	Reserved
		0x1FFE C010 - 0x1FFE FFFF	Reserved
Code	AHB	0x1FFE C000 - 0x1FFE C00F	Reserved
Code	АПБ	0x1001 0000 - 0x1FFE BFFF	Reserved
		0x1000 0000 - 0x1000 FFFF	Reserved
		0x083C 0000 - 0x0FFF FFFF	Reserved
		0x0830 0000 - 0x083B FFFF	Reserved
		0x0810 0000 - 0x082F FFFF	
		0x0802 0000 - 0x080F FFFF	Main Flash
		0x0800 0000 - 0x0801 FFFF	
		0x0030 0000 - 0x07FF FFFF	Reserved
		0x0010 0000 - 0x002F FFFF	Aliased to Main Flash or
		0x0002 0000 - 0x000F FFFF	Boot loader
		0x0000 0000 - 0x0001 FFFF	2001100001



2.5. Clock tree

Figure 2-6. GD32E103xx clock tree



Legend:

HXTAL: 4 to 32 MHz High Speed crystal oscillator LXTAL: 32,768 Hz Low Speed crystal oscillator

IRC8M: Internal 8 MHz RC oscillator IRC40K: Internal 40 KHz RC oscillator IRC48M: Internal 48 MHz RC oscillator

2.6. Pin definitions

Notes:

For GD32E103Rx LQFP64 $_{\smallsetminus}$ GD32E103Cx LQFP48 and GD32E103Tx QFN36, $V_{\text{REF-}}$ and $V_{\text{REF+}}$ are internally connected to V_{SSA} and V_{DDA} respectively.



2.6.1. GD32E103Vx LQFP100 pin definitions

Table 2-3. GD32E103Vx LQFP100 pin definitions

	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
		Typo	20101	Default: PE2
PE2	1	I/O	5VT	Alternate: TRACECK, EXMC_A23
				Default: PE3
PE3	2	I/O	5VT	Alternate: TRACED0, EXMC_A19
				Default: PE4
PE4	3	I/O	5VT	Alternate: TRACED1, EXMC_A20
				Default: PE5
PE5	4	I/O	5VT	Alternate: TRACED2, EXMC_A21
				Remap: TIMER8_CH0
				Default: PE6
PE6	5	I/O	5VT	Alternate: TRACED3, EXMC_A22
				Remap: TIMER8_CH1
V _{BAT}	6	Р	-	Default: V _{BAT}
PC13-				- 4 11 - 2012
TAMPER-	7	I/O	-	Default: PC13
RTC				Alternate: RTC_TAMPER
PC14-		1/0		Default: PC14
OSC32IN	8	I/O	-	Alternate: OSC32IN
PC15-				Defects DOAE
OSC32OU	9	I/O	-	Default: PC15
Т				Alternate: OSC32OUT
V _{SS_5}	10	Р	-	Default: V _{SS_5}
V _{DD_5}	11	Р	-	Default: V _{DD_5}
OSCINI	12		_	Default: OSCIN
OSCIN		I	-	Remap: PD0
OSCOLIT	12	SCOUT 13 O -		Default: OSCOUT
030001	13)	-	Remap:PD1
NRST	14	I/O	-	Default: NRST
PC0	15	I/O	_	Default: PC0
FC0	15	Ŋ	-	Alternate: ADC01_IN10
PC1	16	I/O	_	Default: PC1
101	10	i/O	_	Alternate: ADC01_IN11
PC2	17	I/O	_	Default: PC2
1 02	''	1/ 1/0		Alternate: ADC01_IN12
PC3	18	1/0	I/O -	Default: PC3
	10	1,0		Alternate: ADC01_IN13
V _{SSA}	19	Р	-	Default: V _{SSA}
V_{REF}	20	Р	-	Default: V _{REF} -



			GD32E TU3XX Datastie		
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description	
V_{REF+}	21	Р	-	Default: V _{REF+}	
V_{DDA}	22	Р	-	Default: V _{DDA}	
				Default: PA0	
PA0-WKUP	23	I/O	-	Alternate: WKUP, USART1_CTS, ADC01_IN0,	
				TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI	
				Default: PA1	
PA1	24	I/O	-	Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1,	
				TIMER1_CH1	
				Default: PA2	
PA2	25	I/O	-	Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2,	
				TIMER8_CH0, TIMER1_CH2, SPI0_IO2	
				Default: PA3	
PA3	26	I/O	-	Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3,	
				TIMER1_CH3, TIMER8_CH1, SPI0_IO3	
V_{SS_4}	27	Р	-	Default: V _{SS_4}	
V_{DD_4}	28	Р	-	Default: V _{DD_4}	
				Default: PA4	
PA4	29	I/O		Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,	
FA4	29	1/0	-	ADC01_IN4	
				Remap: SPI2_NSS, I2S2_WS	
PA5	30	I/O		Default: PA5	
FAS	30	Ŋ	-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1	
				Default: PA6	
PA6	31	I/O	_	Alternate: SPI0_MISO, TIMER7_BKIN, ADC01_IN6,	
1 70	51	1/0	_	TIMER2_CH0, TIMER12_CH0	
				Remap: TIMER0_BKIN	
				Default: PA7	
PA7	32	I/O	_	Alternate: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7,	
IAI	52	1/0	_	TIMER2_CH1, TIMER13_CH0	
				Remap: TIMER0_CH0_ON	
PC4	33	I/O	_	Default: PC4	
1 0 4	00	1/0		Alternate: ADC01_IN14	
PC5	34	I/O	_	Default: PC5	
1 03	34	i/O		Alternate: ADC01_IN15	
				Default: PB0	
PB0	35	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON	
				Remap: TIMER0_CH1_ON	
				Default: PB1	
PB1	36	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON	
				Remap: TIMER0_CH2_ON	
PB2	37	I/O	5VT	Default: PB2, BOOT1	



Pin Name			Pin	in 1/0			
PE7 38 I/O	Pin Name	Pins			Functions description		
Remap: TIMERO_ETI					Default: PE7		
Default: PE8	PE7	38	I/O	5VT	Alternate: EXMC_D4		
PE8 39 I/O 5VT Alternate: EXMC_D5 Remap: TIMERO_CHO_ON					Remap: TIMER0_ETI		
Remap: TIMERO_CHO_ON					Default: PE8		
Default: PE9	PE8	39	I/O	5VT	Alternate: EXMC_D5		
PE9					Remap: TIMER0_CH0_ON		
Remap: TIMERO_CH0					Default: PE9		
Default: PE10	PE9	40	I/O	5VT	Alternate: EXMC_D6		
PE10					Remap: TIMER0_CH0		
Remap: TIMERO_CH1_ON					Default: PE10		
Default: PE11	PE10	41	I/O	5VT	Alternate: EXMC_D7		
PE11					Remap: TIMER0_CH1_ON		
Remap: TIMERO_CH1					Default: PE11		
Default: PE12	PE11	42	I/O	5VT	Alternate: EXMC_D8		
PE12					Remap: TIMER0_CH1		
Remap: TIMER0_CH2_ON					Default: PE12		
Default: PE13	PE12	43	I/O	5VT	Alternate: EXMC_D9		
PE13 44 I/O 5VT Alternate: EXMC_D10 Remap: TIMER0_CH2 PE14 45 I/O 5VT Alternate: EXMC_D11 Remap: TIMER0_CH3 PE15 46 I/O 5VT Alternate: EXMC_D12 Remap: TIMER0_BKIN PB10 47 I/O 5VT Alternate: EXMC_D12 Remap: TIMER1_CH2 PB11 48 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 PB11 48 I/O 5VT Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 VbD_1 50 P - Default: PB12 PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13					Remap: TIMER0_CH2_ON		
Remap: TIMER0_CH2					Default: PE13		
PE14 45 I/O 5VT Alternate: EXMC_D11 Remap: TIMER0_CH3 PE15 46 I/O 5VT Alternate: EXMC_D12 Remap: TIMER0_BKIN PB10 47 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 Default: PB10 Default: PB11 Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 Default: Vss_1 Default: PB12 Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13	PE13	44	I/O	5VT	Alternate: EXMC_D10		
PE14 45 I/O 5VT Alternate: EXMC_D11 Remap: TIMER0_CH3 PE15 46 I/O 5VT Alternate: EXMC_D12 Remap: TIMER0_BKIN PB10 47 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 PB11 48 I/O 5VT Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 Vpo_1 50 P - Default: Vpo_1 PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13					Remap: TIMER0_CH2		
Remap: TIMERO_CH3					Default: PE14		
Default: PE15	PE14	45	I/O	5VT	Alternate: EXMC_D11		
PE15 46 I/O 5VT Alternate: EXMC_D12 Remap: TIMER0_BKIN PB10 47 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 PB11 48 I/O 5VT Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 VDD_1 50 P - Default: VDD_1 PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13 Default: PB13					Remap: TIMER0_CH3		
Remap: TIMERO_BKIN					Default: PE15		
Default: PB10 47 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 Default: PB11 Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 VDD_1 50 P - Default: VDD_1 Default: PB12 PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13	PE15	46	I/O	5VT	Alternate: EXMC_D12		
PB10 47 I/O 5VT Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 PB11 48 I/O 5VT Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 VDD_1 50 P - Default: VDD_1 Default: PB12 Default: PB12 Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13					Remap: TIMER0_BKIN		
Remap: TIMER1_CH2					Default: PB10		
Default: PB11	PB10	47	I/O	5VT	Alternate: I2C1_SCL, USART2_TX		
PB11 48 I/O 5VT Alternate: I2C1_SDA, USART2_RX Remap: TIMER1_CH3 Vss_1 49 P - Default: Vss_1 VDD_1 50 P - Default: VDD_1 Default: PB12 Default: PB12 Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13 Default: PB13					Remap: TIMER1_CH2		
Remap: TIMER1_CH3					Default: PB11		
Vss_1 49 P - Default: Vss_1 VDD_1 50 P - Default: VDD_1 Default: PB12 Default: PB12 Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13	PB11	48	I/O	5VT	Alternate: I2C1_SDA, USART2_RX		
VDD_1 50 P - Default: VDD_1 PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMERO_BKIN, CAN1_RX Default: PB13 Default: PB13					Remap: TIMER1_CH3		
PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13	Vss_1	49	Р	-	Default: V _{SS_1}		
PB12 51 I/O 5VT Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK, TIMER0_BKIN, CAN1_RX Default: PB13	V _{DD_1}	50	Р	-	Default: V _{DD_1}		
TIMER0_BKIN, CAN1_RX Default: PB13					Default: PB12		
Default: PB13	PB12	51	I/O	5VT	Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK,		
					TIMER0_BKIN, CAN1_RX		
PB13 52 I/O 5VT Alternate: SPI1 SCK, I2S1 CK USART2 CTS					Default: PB13		
	PB13	52	I/O	5VT	Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,		
TIMERO_CHO_ON, CAN1_TX, I2C1_TXFRAME					TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME		





	Pin I/O		ODOZE 100XX Datasnee	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
				Default: PB14
PB14	53	I/O	5VT	Alternate: SPI1_MISO, USART2_RTS, TIMER0_CH1_ON,
				TIMER11_CH0
				Default: PB15
PB15	54	I/O	5VT	Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,
				TIMER11_CH11
				Default: PD8
PD8	55	I/O	5VT	Alternate: EXMC_D13
				Remap: USART2_TX
				Default: PD9
PD9	56	I/O	5VT	Alternate: EXMC_D14
				Remap: USART2_RX
				Default: PD10
PD10	57	I/O	5VT	Alternate: EXMC_D15
				Remap: USART2_CK
				Default: PD11
PD11	58	I/O	5VT	Alternate: EXMC_A16
				Remap: USART2_CTS
				Default: PD12
PD12	59	I/O	5VT	Alternate: EXMC_A17
				Remap: TIMER3_CH0, USART2_RTS
				Default: PD13
PD13	60	I/O	5VT	Alternate: EXMC_A18
				Remap: TIMER3_CH1
			5VT	Default: PD14
PD14	61	I/O		Alternate: EXMC_D0
				Remap: TIMER3_CH2
				Default: PD15
PD15	62	I/O	5VT	Alternate: EXMC_D1
				Remap: TIMER3_CH3, CTC_SYNC
				Default: PC6
PC6	63	I/O	5VT	Alternate: I2S1_MCK, TIMER7_CH0
				Remap: TIMER2_CH0
			_, _	Default: PC7
PC7	64	I/O	5VT	Alternate: I2S2_MCK, TIMER7_CH1
				Remap: TIMER2_CH1
200			<u></u>	Default: PC8
PC8	65	I/O	5VT	Alternate: TIMER7_CH2
				Remap: TIMER2_CH2



				GD32E T03XX Datasnee
Pin Name	Pins	Pin	I/O	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	
				Default: PC9
PC9	66	I/O	5VT	Alternate: TIMER7_CH3
				Remap: TIMER2_CH3
				Default: PA8
PA8	67	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, VCORE,
				USBFS_SOF, CTC_SYNC
DAG	00	1/0	c) /T	Default: PA9
PA9	68	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
				Default: PA10
PA10	69	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID, V1REF
				Default: PA11
PA11	70	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,
				TIMER0_CH3
				Default: PA12
PA12	71	I/O	5VT	Alternate: USARTO_RTS, CANO_TX, USBFS_DP,
		., 0		TIMERO_ETI
				Default: JTMS, SWDIO
PA13	72	I/O	5VT	Remap: PA13
NC	73	_	_	- Tronger in Arts
V _{SS_2}	74	- Р		Default: V _{SS 2}
			-	-
V_{DD_2}	75	Р	-	Default: V _{DD_2}
PA14	76	I/O	5VT	Default: JTCK, SWCLK
				Remap:PA14
				Default: JTDI
PA15	77	I/O	5VT	Alternate: SPI2_NSS, I2S2_WS
				Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
				Default: PC10
PC10	78	I/O	5VT	Alternate: UART3_TX
				Remap: USART2_TX, SPI2_SCK, I2S2_CK
				Default: PC11
PC11	79	I/O	5VT	Alternate: UART3_RX
				Remap: USART2_RX, SPI2_MISO
				Default: PC12
PC12	80	I/O	5VT	Alternate: UART4_TX
				Remap: USART2_CK, SPI2_MOSI, I2S2_SD
				Default: PD0
PD0	81	I/O	5VT	Alternate: EXMC_D2
				Remap: OSCIN, CAN0_RX
				Default: PD1
PD1	82	I/O	5VT	Alternate: EXMC_D3
				Remap: OSCOUT, CAN0_TX
<u> </u>				<u>l</u>



Pin Name		Pin I/O			
PD2	Pin Name	Pins			Functions description
Alternate: TIMER2_ETI, UART4_RX	DD3	02	1/0	E\/T	Default: PD2
PD3	FDZ	03	Ŋ	371	Alternate: TIMER2_ETI, UART4_RX
Remap: USART1_CTS					Default: PD3
Default: PD4	PD3	84	I/O	5VT	Alternate: EXMC_CLK
PD4					Remap: USART1_CTS
Remap: USART1_RTS					Default: PD4
Default: PD5	PD4	85	I/O	5VT	Alternate: EXMC_NOE
PD5					Remap: USART1_RTS
Remap: USART1_TX					Default: PD5
Default: PD6 RT I/O SVT Alternate: EXMC_NWAIT Remap: USART1_RX	PD5	86	I/O	5VT	Alternate: EXMC_NWE
PD6					Remap: USART1_TX
Remap: USART1_RX					Default: PD6
Default: PD7	PD6	87	I/O	5VT	Alternate: EXMC_NWAIT
PD7					Remap: USART1_RX
Remap: USART1_CK					Default: PD7
Default: JTDO	PD7	88	I/O	5VT	Alternate: EXMC_NE0
PB3 89 I/O 5VT Alternate: SPI2_SCK, I2S2_CK Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK Default: NJTRST PB4 90 I/O 5VT Alternate: SPI2_MISO, I2C0_TXFRAME Remap: TIMER2_CH0, PB4, SPI0_MISO Default: PB5 PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX Default: PB6 PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 Default: PB7 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 Default: B0OT0 Default: PB8 Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX Default: PB9 PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX Default: PE0 Default: PE0					Remap: USART1_CK
Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK					Default: JTDO
Default: NJTRST	PB3	89	I/O	5VT	Alternate: SPI2_SCK, I2S2_CK
PB4 90 I/O 5VT Alternate: SPI2_MISO, I2C0_TXFRAME Remap: TIMER2_CH0, PB4, SPI0_MISO PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 Default: PB8 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0					Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK
Remap: TIMER2_CH0, PB4, SPI0_MISO				5VT	Default: NJTRST
Default: PB5	PB4	90	I/O		Alternate: SPI2_MISO, I2C0_TXFRAME
PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0					Remap: TIMER2_CH0, PB4, SPI0_MISO
Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX					Default: PB5
PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0	PB5	91	I/O	-	Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD
PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0					Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
Remap: USART0_TX, CAN1_TX, SPI0_IO2					Default: PB6
Default: PB7	PB6	92	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0
PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX Default: PB9 PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX Default: PE0					Remap: USART0_TX, CAN1_TX, SPI0_IO2
Remap: USARTO_RX, SPIO_IO3					Default: PB7
BOOT0 94 I - Default: BOOT0	PB7	93	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV)
PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0					Remap: USART0_RX, SPI0_IO3
PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0	воото	94	I	-	Default: BOOT0
Remap: I2C0_SCL, CAN0_RX					Default: PB8
PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0	PB8	95	I/O	5VT	Alternate: TIMER3_CH2, TIMER9_CH0
PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0					Remap: I2C0_SCL, CAN0_RX
Remap: I2C0_SDA, CAN0_TX					Default: PB9
PE0 97 I/O 5VT Default:PE0	PB9	96	I/O	5VT	Alternate: TIMER3_CH3, TIMER10_CH0
PE0 97 I/O 5VT Default:PE0					Remap: I2C0_SDA, CAN0_TX
PE0 97 I/O 5VT Alternate: TIMER3_ETI, EXMC_NBL0				_,	Default:PE0
	PE0	97	I/O	5VT	Alternate: TIMER3_ETI, EXMC_NBL0



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PE1	98	I/O	5VT	Default: PE1 Alternate: EXMC_NBL1
V _{SS_3}	99	Р	1	Default: V _{SS_3}
V_{DD_3}	100	Р	-	Default: V _{DD_3}

Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. Functions are available in GD32E103xx devices.

2.6.2. GD32E103Rx LQFP64 pin definitions

Table 2-4. GD32E103Rx LQFP64 pin definitions

		Pin	I/O	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
V _{BAT}	1	Р	-	Default: V _{BAT}
PC13- TAMPER- RTC	2	I/O	-	Default: PC13 Alternate: RTC_TAMPER
PC14- OSC32IN	3	I/O	-	Default: PC14 Alternate:OSC32IN
PC15- OSC32OUT	4	I/O	-	Default: PC15 Alternate:OSC32OUT
PD0-OSCIN	5	-	-	Default: OSCIN Remap: PD0 ⁽³⁾
PD1- OSCOUT	6	0	-	Default: OSCOUT Remap: PD1 ⁽³⁾
NRST	7	I/O	-	Default: NRST
PC0	8	I/O	-	Default: PC0 Alternate: ADC01_IN10
PC1	9	I/O	-	Default: PC1 Alternate: ADC01_IN11
PC2	10	I/O	-	Default: PC2 Alternate: ADC01_IN12
PC3	11	I/O	-	Default: PC3 Alternate: ADC01_IN13
Vssa	12	Р	-	Default: Vssa
V_{DDA}	13	Р	-	Default: V _{DDA}
PA0-WKUP	14	I/O	-	Default: PA0 Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI
PA1	15	I/O	-	Default: PA1



				GD32E103xx Datasnee
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1,
				TIMER1_CH1
				Default: PA2
PA2	16	I/O	-	Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2,
				TIMER8_CH0, TIMER1_CH2, SPI0_IO2
				Default: PA3
PA3	17	I/O	-	Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3,
				TIMER1_CH3, TIMER8_CH1, SPI0_IO3
V _{SS_4}	18	Р	-	Default: Vss_4
V _{DD_4}	19	Р	-	Default: V _{DD_4}
				Default: PA4
DA4	20	1/0		Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
PA4	20	I/O	-	ADC01_IN4
				Remap: SPI2_NSS, I2S2_WS
DAG	24	1/0		Default: PA5
PA5	21	I/O	-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
				Default: PA6
DAG	00	1/0		Alternate: SPI0_MISO, TIMER7_BKIN, ADC01_IN6,
PA6	22	I/O	-	TIMER2_CH0, TIMER12_CH0
				Remap: TIMER0_BKIN
				Default: PA7
PA7	22	I/O		Alternate: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7,
PAI	23	1/0	-	TIMER2_CH1, TIMER13_CH0
				Remap: TIMER0_CH0_ON
DC4	24	I/O		Default: PC4
PC4	24	1/0	-	Alternate: ADC01_IN14
PC5	25	I/O		Default: PC5
PCS	23	Ŋ	_	Alternate: ADC01_IN15
				Default: PB0
PB0	26	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON
				Remap: TIMER0_CH1_ON
				Default: PB1
PB1	27	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON
				Remap: TIMER0_CH2_ON
PB2	28	I/O	5VT	Default: PB2, BOOT1
				Default: PB10
PB10	29	I/O	5VT	Alternate: I2C1_SCL, USART2_TX
				Remap: TIMER1_CH2
				Default: PB11
PB11	30	I/O	5VT	Alternate: I2C1_SDA, USART2_RX
				Remap: TIMER1_CH3



		Pin	Wo GD32E 103XX Datastie	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
Vss_1	31	Р	-	Default: V _{SS_1}
V_{DD_1}	32	Р	-	Default: V _{DD_1}
				Default: PB12
PB12	33	I/O	5VT	Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK,
				TIMER0_BKIN, CAN1_RX
				Default: PB13
PB13	34	I/O	5VT	Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,
				TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME
				Default: PB14
PB14	35	I/O	5VT	Alternate: SPI1_MISO, USART2_RTS, TIMER0_CH1_ON,
				TIMER11_CH0
				Default: PB15
PB15	36	I/O	5VT	Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,
				TIMER11_CH11
				Default: PC6
PC6	37	I/O	5VT	Alternate: I2S1_MCK, TIMER7_CH0
				Remap: TIMER2_CH0
				Default: PC7
PC7	38	I/O	5VT	Alternate: I2S2_MCK, TIMER7_CH1
				Remap: TIMER2_CH1
				Default: PC8
PC8	39	I/O	5VT	Alternate: TIMER7_CH2
				Remap: TIMER2_CH2
				Default: PC9
PC9	40	I/O	5VT	Alternate: TIMER7_CH3
				Remap: TIMER2_CH3
				Default: PA8
PA8	41	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, VCORE,
				USBFS_SOF, CTC_SYNC
PA9	42	I/O	5VT	Default: PA9
1710		., 0		Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
PA10	43	I/O	5VT	Default: PA10
17110	10	., 0	011	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID, V1REF
				Default: PA11
PA11	44	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,
				TIMER0_CH3
				Default: PA12
PA12	45	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,
				TIMER0_ETI
PA13	46	I/O	5VT	Default: JTMS, SWDIO
17(10	+0)	J V I	Remap: PA13



			GD32E 103XX Datasne		
Pin Name	Pins	Pin	I/O	Functions description	
		Type ⁽¹⁾	Level ⁽²⁾	T direction descentification	
Vss_2	47	Р	-	Default: V _{SS_2}	
V_{DD_2}	48	Р	-	Default: V _{DD_2}	
PA14	49	I/O	5VT	Default: JTCK, SWCLK	
ra 14	49	1/0	371	Remap:PA14	
				Default: JTDI	
PA15	50	I/O	5VT	Alternate: SPI2_NSS, I2S2_WS	
				Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15, SPI0_NSS	
				Default: PC10	
PC10	51	I/O	5VT	Alternate: UART3_TX	
				Remap: USART2_TX, SPI2_SCK, I2S2_CK	
				Default: PC11	
PC11	52	I/O	5VT	Alternate: UART3_RX	
				Remap: USART2_RX, SPI2_MISO	
				Default: PC12	
PC12	53	I/O	5VT	Alternate: UART4_TX	
				Remap: USART2_CK, SPI2_MOSI, I2S2_SD	
DD:		.,0	-> / -	Default: PD2	
PD2	54	I/O	5VT	Alternate: TIMER2_ETI, UART4_RX	
				Default: JTDO	
PB3	55	I/O	5VT	Alternate: SPI2_SCK, I2S2_CK	
				Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK	
				Default: NJTRST	
PB4	56	I/O	5VT	Alternate: SPI2_MISO, I2C0_TXFRAME	
				Remap: TIMER2_CH0, PB4, SPI0_MISO	
				Default: PB5	
PB5	57	I/O	-	Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD	
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX	
				Default: PB6	
PB6	58	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0	
				Remap: USART0_TX, CAN1_TX, SPI0_IO2	
				Default: PB7	
PB7	59	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1	
				Remap: USART0_RX, SPI0_IO3	
ВООТ0	60	ı	_	Default: BOOT0	
		•		Default: PB8	
PB8	61	I/O	5VT	Alternate: TIMER3_CH2, TIMER9_CH0	
				Remap: I2C0_SCL, CAN0_RX	
				Default: PB9	
PB9	62	I/O	5VT	Alternate: TIMER3_CH3, TIMER10_CH0	
		"0	J V I	Remap: I2C0_SDA, CAN0_TX	
V _{SS_3}	63	Р	_	Default: Vss_3	
¥ 00_3		· .	<u> </u>	Delault. VSS_3	



	Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
ĺ	V_{DD_3}	64	Р	-	Default: V _{DD_3}

Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. PD0/PD1 cannot be used for EXTI in this package.

2.6.3. GD32E103Cx LQFP48 pin definitions

Table 2-5. GD32E103Cx LQFP48 pin definitions

Table 2-5. GD		Pin	I/O	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
V _{BAT}	1	Р	-	Default: V _{BAT}
PC13-				Default: PC13
TAMPER-	2	I/O	-	Alternate: RTC_TAMPER
RTC				
PC14-	3	I/O	-	Default: PC14
OSC32IN				Alternate:OSC32IN
PC15-	4	I/O	-	Default: PC15
OSC32OUT		1,0		Alternate:OSC32OUT
PD0-OSCIN	5	1	-	Default: OSCIN
				Remap: PD0 ⁽³⁾
PD1-OSCOUT	6	0	-	Default: OSCOUT
				Remap: PD1 ⁽³⁾
NRST	7	I/O	-	Default: NRST
Vssa	8	Р	-	Default: V _{SSA}
V _{DDA}	9	Р	-	Default: V _{DDA}
				Default: PA0
PA0-WKUP	10	I/O	-	Alternate: WKUP, USART1_CTS, ADC01_IN0,
				TIMER1_CH0_ETI, TIMER4_CH0
				Default: PA1
PA1	11	I/O	-	Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1,
				TIMER1_CH1
				Default: PA2
PA2	12	I/O	-	Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2,
				TIMER8_CH0, TIMER1_CH2, SPI0_IO2
				Default: PA3
PA3	13	I/O	-	Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3,
				TIMER1_CH3, TIMER8_CH1, SPI0_IO3
				Default: PA4
PA4	14	I/O	-	Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
				ADC01_IN4



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Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description		
				Remap: SPI2_NSS, I2S2_WS		
PA5	15	I/O	_	Default: PA5		
FAS	15	1/0	-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1		
				Default: PA6		
PA6	16	I/O		Alternate: SPI0_MISO, ADC01_IN6, TIMER2_CH0,		
FAO	10	1/0	-	TIMER12_CH0		
				Remap: TIMER0_BKIN		
				Default: PA7		
PA7	17	I/O	_	Alternate: SPI0_MOSI, ADC01_IN7, TIMER2_CH1,		
	''	1/0	_	TIMER13_CH0		
				Remap: TIMER0_CH0_ON		
				Default: PB0		
PB0	18	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2		
				Remap: TIMER0_CH1_ON		
				Default: PB1		
PB1	19	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3		
				Remap: TIMER0_CH2_ON		
PB2	20	I/O	5VT	Default: PB2, BOOT1		
	21	I/O	5VT	Default: PB10		
PB10				Alternate: I2C1_SCL, USART2_TX		
				Remap: TIMER1_CH2		
				Default: PB11		
PB11	22	I/O	5VT	Alternate: I2C1_SDA, USART2_RX		
				Remap: TIMER1_CH3		
Vss_1	23	Р	-	Default: Vss_1		
V _{DD_1}	24	Р	-	Default: V _{DD_1}		
				Default: PB12		
PB12	25	I/O	5VT	Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA,		
				USART2_CK, TIMER0_BKIN, CAN1_RX		
	26	I/O		Default: PB13		
PB13				Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,		
				TIMERO_CHO_ON, CAN1_TX, I2C1_TXFRAME		
	27	I/O	5VT	Default: PB14		
PB14				Alternate: SPI1_MISO, USART2_RTS,		
				TIMER0_CH1_ON, TIMER11_CH0		
	28	I/O	5VT	Default: PB15		
PB15				Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,		
				TIMER11_CH11		
		I/O		Default: PA8		
PA8	29			Alternate: USART0_CK, TIMER0_CH0, CK_OUT0,		
				VCORE, USBFS_SOF, CTC_SYNC		



			r • =	GD32E 103XX Datasneet		
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description		
540		./0	5) (T	Default: PA9		
PA9	30	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS		
				Default: PA10		
PA10	31	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID,		
				V1REF		
				Default: PA11		
PA11	32	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,		
				TIMER0_CH3		
				Default: PA12		
PA12	33	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,		
				TIMER0_ETI		
PA13	34	I/O	5VT	Default: JTMS, SWDIO		
PAIS	34	1/0	371	Remap: PA13		
V _{SS_2}	35	Р	-	Default: V _{SS_2}		
V_{DD_2}	36	Р	ı	Default: V _{DD_2}		
PA14	37	I/O	5VT	Default: JTCK, SWCLK		
PA14	31	1/0	371	Remap:PA14		
		I/O	5VT	Default: JTDI		
PA15	38			Alternate: SPI2_NSS, I2S2_WS		
FAIS	30			Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15,		
				SPI0_NSS		
		I/O	5VT	Default: JTDO		
PB3	39			Alternate: SPI2_SCK, I2S2_CK		
				Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK		
				Default: NJTRST		
PB4	40	I/O	5VT	Alternate: SPI2_MISO, I2C0_TXFRAME		
				Remap: TIMER2_CH0, PB4, SPI0_MISO		
				Default: PB5		
PB5	41	I/O	-	Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD		
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX		
		I/O	5VT	Default: PB6		
PB6	42			Alternate: I2C0_SCL, TIMER3_CH0		
				Remap: USART0_TX, CAN1_TX, SPI0_IO2		
		I/O		Default: PB7		
PB7	43			Alternate: I2C0_SDA, TIMER3_CH1		
				Remap: USART0_RX, SPI0_IO3		
воото	44	I	-	Default: BOOT0		
	45	I/O	5VT	Default: PB8		
PB8				Alternate: TIMER3_CH2, TIMER9_CH0		
				Remap: I2C0_SCL, CAN0_RX		
PB9	46	I/O	5VT	Default: PB9		



	Pin Name	Pins	Pin	I/O	Functions description	
		Type ⁽¹⁾		Level ⁽²⁾		
					Alternate: TIMER3_CH3, TIMER10_CH0	
					Remap: I2C0_SDA, CAN0_TX	
Ī	V_{SS_3}	47	Р	-	Default: V _{SS_3}	
Ī	V_{DD_3}	48	Р	-	Default: V _{DD_3}	

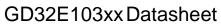
Notes:

- 1. Type: I = input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. PD0/PD1 cannot be used for EXTI in this package.

2.6.4. GD32E103Tx QFN36 pin definitions

Table 2-6. GD32E103Tx LQFP36 pin definitions

Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
DD 2 000111		I	-	Default: OSCIN
PD0-OSCIN	2			Remap: PD0 ⁽³⁾
PD1-OSCOUT	3	0		Default: OSCOUT
PD1-03C001	3	O	-	Remap: PD1 ⁽³⁾
NRST	4	I/O	-	Default: NRST
V_{SSA}	5	Р	-	Default: V _{SSA}
V_{DDA}	6	Р	-	Default: V _{DDA}
		I/O		Default: PA0
PA0-WKUP	7		-	Alternate: WKUP, USART1_CTS, ADC01_IN0,
				TIMER1_CH0_ETI, TIMER4_CH0
		I/O	-	Default: PA1
PA1	8			Alternate: USART1_RTS, ADC01_IN1,
				TIMER4_CH1, TIMER1_CH1
				Default: PA2
PA2	9	I/O	-	Alternate: USART1_TX, TIMER4_CH2,
				ADC01_IN2, TIMER1_CH2, SPI0_IO2
				Default: PA3
PA3	10	I/O	-	Alternate: USART1_RX, TIMER4_CH3,
				ADC01_IN3, TIMER1_CH3, SPI0_IO3
				Default: PA4
PA4	11	I/O	-	Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
				ADC01_IN4
PA5	12	I/O	-	Default: PA5
. 7.0	12			Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
		I/O	-	Default: PA6
PA6	13			Alternate: SPI0_MISO, ADC01_IN6, TIMER2_CH0
				Remap: TIMER0_BKIN





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Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PA7	14	I/O	-	Default: PA7 Alternate: SPI0_MOSI, ADC01_IN7, TIMER2_CH1 Remap: TIMER0_CH0_ON
PB0	15	I/O	-	Default: PB0 Alternate: ADC01_IN8, TIMER2_CH2 Remap: TIMER0_CH1_ON
PB1	16	I/O	-	Default: PB1 Alternate: ADC01_IN9, TIMER2_CH3 Remap: TIMER0_CH2_ON
PB2	17	I/O	5VT	Default: PB2, BOOT1
V _{SS_1}	18	Р	-	Default: V _{SS_1}
V _{DD_1}	19	Р	-	Default: V _{DD_1}
PA8	20	I/O	5VT	Default: PA8 Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, VCORE, USBFS_SOF, CTC_SYNC
PA9	21	I/O	5VT	Default: PA9 Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
PA10	22	I/O	5VT	Default: PA10 Alternate: USART0_RX, TIMER0_CH2, USBFS_ID, V1REF
PA11	23	I/O	5VT	Default: PA11 Alternate: USART0_CTS, CAN0_RX, USBFS_DM, TIMER0_CH3
PA12	24	I/O	5VT	Default: PA12 Alternate: USART0_RTS, CAN0_TX, USBFS_DP, TIMER0_ETI
PA13	25	I/O	5VT	Default: JTMS, SWDIO Remap: PA13
Vss_2	26	Р	-	Default: Vss_2
V _{DD_2}	27	Р	-	Default: V _{DD_2}
PA14	28	I/O	5VT	Default: JTCK, SWCLK Remap:PA14
PA15	29	I/O	5VT	Default: JTDI Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15, SPI0_NSS
PB3	30	I/O	5VT	Default: JTDO Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK
PB4	31	I/O	5VT	Default: NJTRST Alternate: I2C0_TXFRAME



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Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Remap: TIMER2_CH0, PB4, SPI0_MISO
				Default: PB5
PB5	32	I/O	-	Alternate: I2C0_SMBA
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
				Default: PB6
PB6	33	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0
				Remap: USART0_TX, CAN1_TX, SPI0_IO2
				Default: PB7
PB7	34	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1
				Remap: USART0_RX, SPI0_IO3
воото	35	ı	-	Default: BOOT0
V _{SS_3}	36	Р	-	Default: V _{SS_3}
V _{DD_3}	1	Р	-	Default: V _{DD_3}

Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. PD0/PD1 cannot be used for EXTI in this package.



3. Functional description

3.1. ARM[®] Cortex[™]-M4 core

The ARM® Cortex®-M4 processor is a high performance embedded processor with DSP instructions which allow efficient signal processing and complex algorithm execution. It brings an efficient, easy-to-use blend of control and signal processing capabilities to meet the digital signal control markets demand. The processor is highly configurable enabling a wide range of implementations from those requiring floating point operations, memory protection and powerful trace technology to cost sensitive devices requiring minimal area, while delivering outstanding computational performance and an advanced system response to interrupts.

32-bit ARM® Cortex®-M4 processor core

- Up to 120 MHz operation frequency
- Single-cycle multiplication and hardware divider
- Floating Point Unit (FPU)
- Integrated DSP instructions
- Integrated Nested Vectored Interrupt Controller (NVIC)
- 24-bit SysTick timer

The Cortex®-M4 processor is based on the ARMv7-M architecture and supports both Thumb and Thumb-2 instruction sets. Some system peripherals listed below are also provided by Cortex®-M4:

- Internal Bus Matrix connected with ICode bus, DCode bus, system bus, Private Peripheral Bus (PPB) and debug accesses (AHB-AP)
- Nested Vectored Interrupt Controller (NVIC)
- Flash Patch and Breakpoint (FPB)
- Data Watchpoint and Trace (DWT)
- Instrument Trace Macrocell (ITM)
- Serial Wire JTAG Debug Port (SWJ-DP)
- Trace Port Interface Unit (TPIU)

3.2. On-chip memory

- Up to 128 Kbytes of Flash memory
- Up to 32 KB of SRAM

The ARM® Cortex®-M4 processor is structured in Harvard architecture which can use separate buses to fetch instructions and load/store data. 128 Kbytes of inner Flash at most, which includes code Flash that available for storing programs and data, and accessed (R/W) at CPU clock speed with zero wait states. An extra data Flash is also included for storing data mainly. *Table 2-2. GD32E103xx memory map* shows the memory of the GD32E103xx series of devices, including Flash, SRAM, peripheral, and other pre-defined regions.



3.3. Clock, reset and supply management

- Internal 8 MHz factory-trimmed RC and external 4 to 32 MHz crystal oscillator
- Internal 48 MHz RC oscillator
- Internal 40 KHz RC calibrated oscillator and external 32.768 KHz crystal oscillator
- 1.71 to 3.6 V application supply and I/Os
- Supply Supervisor: POR (Power On Reset), PDR (Power Down Reset), and low voltage detector (LVD)

The Clock Control Unit (CCU) provides a range of oscillator and clock functions. These include internal RC oscillator and external crystal oscillator, high speed and low speed two types. Several prescalers allow the frequency configuration of the AHB and two APB domains. The maximum frequency of the two AHB domains are 120MHz. The maximum frequency of the two APB domains including APB1 is 60 MHz and APB2 is 120 MHz. See *Figure 2-6. GD32E103xx clock tree* for details on the clock tree.

The Reset Control Unit (RCU) controls three kinds of reset: system reset resets the processor core and peripheral IP components. Power-on reset (POR) and power-down reset (PDR) are always active, and ensures proper operation starting from 1.66V/down to 1.62V. The device remains in reset mode when V_{DD} is below a specified threshold. The embedded low voltage detector (LVD) monitors the power supply, compares it to the voltage threshold and generates an interrupt as a warning message for leading the MCU into security.

Power supply schemes:

- V_{DD} range: 1.71 to 3.6 V, external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- VDDA range: 1.71 to 3.6 V, external analog power supplies for ADC, reset blocks, RCs and PLL VDDA and VssA must be connected to VDD and Vss, respectively.
- VBAT range: 1.71 to 3.6 V, power supply for RTC, external clock 32.768 KHz oscillator and backup registers (through power switch) when VDD is not present.

3.4. Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from main flash memory (default)
- Boot from system memory
- Boot from on-chip SRAM

In default condition, boot from main Flash memory is selected. The boot loader is located in the internal boot ROM memory (system memory). It is used to reprogram the Flash memory by using USART0 (PA9 and PA10).



3.5. Power saving modes

The MCU supports three kinds of power saving modes to achieve even lower power consumption. They are Sleep mode, Deep-sleep mode, and Standby mode. These operating modes reduce the power consumption and allow the application to achieve the best balance between the CPU operating time, speed and power consumption.

■ Sleep mode

In sleep mode, only the clock of CPU core is off. All peripherals continue to operate and any interrupt/event can wake up the system.

■ **Deep-sleep** mode

In deep-sleep mode, all clocks in the 1.2V domain are off, and all of the high speed crystal oscillator (IRC8M, IRC48M, HXTAL) and PLL are disabled. Only the contents of SRAM and registers are retained. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, the LVD output, and USB wakeup. When exiting the deep-sleep mode, the IRC8M is selected as the system clock.

■ Standby mode

In standby mode, the whole 1.2V domain is power off, the LDO is shut down, and all of IRC8M, IRC48M, HXTAL and PLL are disabled. The contents of SRAM and registers (except Backup Registers) are lost. There are four wakeup sources for the standby mode, including the external reset from NRST pin, the RTC, the FWDG reset, and the rising edge on WKUP pin.

3.6. Analog to digital converter (ADC)

- 12-bit SAR ADC's conversion rate is up to 3 MSPS
- 12-bit, 10-bit, 8-bit or 6-bit configurable resolution
- Hardware oversampling ratio adjustable from 2 to 256x improves resolution to 16-bit
- Input voltage range: VREF- to VREF+
- Temperature sensor

Up to two 12-bit 3 MSPS multi-channel ADCs are integrated in the device. It has a total of 18 multiplexed channels: 16 external channels, 1 channel for internal temperature sensor (V_{SENSE}), 1 channel for internal reference voltage (V_{REFINT}, V_{REFINT} = 1.2V). The input voltage range is from V_{REF-} to V_{REF+}. An on-chip hardware oversampling scheme improves performance while off-loading the related computational burden from the CPU. An analog watchdog block can be used to detect the channels, which are required to remain within a specific threshold window. A configurable channel management block can be used to perform conversions in single, continuous, scan or discontinuous mode to support more advanced use.

The ADC can be triggered from the events generated by the general level 0 timers (TIMERx, x=1, 2, 3) and the advanced timers (TIMER0 and TIMER7) with internal connection. The



temperature sensor can be used to generate a voltage that varies linearly with temperature. It is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage in a digital value.

3.7. Digital to analog converter (DAC)

- 12-bit DAC with independent output channels
- 8-bit or 12-bit mode in conjunction with the DMA controller

The 12-bit buffered DAC is used to generate variable analog outputs. The DAC channels can be triggered by the timer or EXTI with DMA support. In dual DAC channel operation, conversions could be done independently or simultaneously. The maximum output value of the DAC is VREF+.

3.8. DMA

- 7 channel DMA0 controller and 5 channel DMA1 controller
- Peripherals supported: Timers, ADC, SPIs, I2Cs, USARTs, DAC, I2S

The flexible general-purpose DMA controllers provide a hardware method of transferring data between peripherals and/or memory without intervention from the CPU, thereby freeing up bandwidth for other system functions. Three types of access method are supported: peripheral to memory, memory to peripheral, memory to memory.

Each channel is connected to fixed hardware DMA requests. The priorities of DMA channel requests are determined by software configuration and hardware channel number. Transfer size of source and destination are independent and configurable.

3.9. General-purpose inputs/outputs (GPIOs)

- Up to 80 fast GPIOs, all mappable on 16 external interrupt lines
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 80 general purpose I/O pins (GPIO) in GD32E103xx, named PA0 ~ PA15, PB0 ~ PB15, PC0 ~ PC15, PD0 ~ PD15 and PE0 ~ PE15 to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The external interrupts on the GPIO pins of the device have related control and configuration registers in the Interrupt/event controller (EXTI). The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current capable except for analog inputs.



3.10. Timers and PWM generation

- Two 16-bit advanced timer (TIMER0 & TIMER7), ten 16-bit general timers (TIMER1 ~ TIMER4, TIMER8 ~ TIMER13), and two 16-bit basic timer (TIMER5 & TIMER6)
- Up to 4 independent channels of PWM, output compare or input capture for each general timer and external trigger input
- 16-bit, motor control PWM advanced timer with programmable dead-time generation for output match
- Encoder interface controller with two inputs using quadrature decoder
- 24-bit SysTick timer down counter
- 2 watchdog timers (free watchdog timer and window watchdog timer)

The advanced timer (TIMER0 & TIMER7) can be used as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable dead-time generation. It can also be used as a complete general timer. The 4 independent channels can be used for input capture, output compare, PWM generation (edge-aligned or center-aligned counting modes) and single pulse mode output. If configured as a general 16-bit timer, it has the same functions as the TIMERx timer. It can be synchronized with external signals or to interconnect with other general timers together which have the same architecture and features.

The general timer, can be used for a variety of purposes including general time, input signal pulse width measurement or output waveform generation such as a single pulse generation or PWM output, up to 4 independent channels for input capture/output compare. TIMER1 ~ TIMER4 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. TIMER8 ~ TIMER13 is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. The general timer also supports an encoder interface with two inputs using quadrature decoder.

The basic timer, known as TIMER5 &TIMER6, are mainly used for DAC trigger generation. They can also be used as a simple 16-bit time base.

The GD32E103xx have two watchdog peripherals, free watchdog timer and window watchdog timer. They offer a combination of high safety level, flexibility of use and timing accuracy.

The free watchdog timer includes a 12-bit down-counting counter and an 8-bit prescaler. It is clocked from an independent 40 KHz internal RC and as it operates independently of the main clock, it can operate in deep-sleep and standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management.

The window watchdog timer is based on a 7-bit down counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early wakeup interrupt capability and the counter can be frozen in debug mode.

The SysTick timer is dedicated for OS, but could also be used as a standard down counter. It features:



- A 24-bit down counter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

3.11. Real time clock (RTC)

- 32-bit up-counter with a programmable 20-bit prescaler
- Alarm function
- Interrupt and wake-up event

The real time clock is an independent timer which provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and an expected interrupt. The RTC features a 32-bit programmable counter for long-term measurement using the compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 KHz from external crystal oscillator.

3.12. Inter-integrated circuit (I2C)

- Up to two I2C bus interfaces can support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode

The I2C interface is an internal circuit allowing communication with an external I2C interface which is an industry standard two line serial interface used for connection to external hardware. These two serial lines are known as a serial data line (SDA) and a serial clock line (SCL). The I2C module provides several data transfer rates: up to 100 KHz of standard mode, up to 400 KHz of the fast mode and up to 1 MHz of the fast mode plus. The I2C module also has an arbitration detect function to prevent the situation where more than one master attempts to transmit data to the I2C bus at the same time. A CRC-8 calculator is also provided in I2C interface to perform packet error checking for I2C data.

3.13. Serial peripheral interface (SPI)

- Up to three SPI interfaces with a frequency of up to 30 MHz
- Support both master and slave mode
- Hardware CRC calculation and transmit automatic CRC error checking
- Quad-SPI configuration available in master mode (only in SPI0)
- SPI TI mode and NSS pulse mode supported



The SPI interface uses 4 pins, among which are the serial data input and output lines (MISO & MOSI), the clock line (SCK) and the slave select line (NSS). Both SPIs can be served by the DMA controller. The SPI interface may be used for a variety of purposes, including simplex synchronous transfers on two lines with a possible bidirectional data line or reliable communication using CRC checking.

3.14. Universal synchronous asynchronous receiver transmitter (USART)

- Up to three USARTs and two UARTs with operating frequency up to 7.5MBits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- USARTs support ISO 7816-3 compliant smart card interface

The USART (USART0, USART1 and USART2) and UART (UART3 & UART4) are used to translate data between parallel and serial interfaces, provides a flexible full duplex data exchange using synchronous or asynchronous transfer. It is also commonly used for RS-232 standard communication. The USART/UART includes a programmable baud rate generator which is capable of dividing the system clock to produce a dedicated clock for the USART transmitter and receiver. The USART/UART also supports DMA function for high speed data communication except UART4.

3.15. Inter-IC sound (I2S)

- Two I2S bus interfaces with sampling frequency from 8 KHz to 192 KHz
- Support either master or slave mode

The Inter-IC sound (I2S) bus provides a standard communication interface for digital audio applications by 3-wire serial lines. GD32E103xx contain two I2S-bus interfaces that can be operated with 16/32 bit resolution in master or slave mode, pin multiplexed with SPI1 and SPI2. The audio sampling frequency from 8 KHz to 192 KHz is supported.

3.16. Universal serial bus full-speed interface (USBFS)

- One full-speed USB Interface with frequency up to 12 Mbit/s
- Internal 48 MHz oscillator support crystal-less operation
- Internal main PLL for USB CLK compliantly

The Universal Serial Bus (USB) is a 4-wire bus with 4 bidirectional endpoints. The device controller enables 12 Mbit/s data exchange with integrated transceivers. Transaction formatting is performed by the hardware, including CRC generation and checking. It supports



device modes. The status of a completed USB transfer or error condition is indicated by status registers. An interrupt is also generated if enabled. The required precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use an HXTAL crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode that allows crystalless operation.

3.17. Controller area network (CAN)

- Two CAN interface supports the CAN protocols version 2.0A, 2.0B, ISO11891-1:2015 and BOSCH CAN FD specification with communication frequency up to 1 Mbit/s of classic frames and 6 Mbit/s of FD frames
- Internal main PLL for CAN CLK compliantly

Controller area network (CAN) is a method for enabling serial communication in field bus. The CAN protocol has been used extensively in industrial automation and automotive applications. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three mailboxes for transmission and two FIFOs of three message deep for reception. It also provides 28 scalable/configurable identifier filter banks for selecting the incoming messages needed and discarding the others.

3.18. External memory controller (EXMC)

- Supported external memory: SRAM, PSRAM, ROM and NOR-Flash
- Up to 16-bit data bus
- Support to interface with Motorola 6800 and Intel 8080 type LCD directly

External memory controller (EXMC) is an abbreviation of external memory controller. It is divided in to several sub-banks for external device support, each sub-bank has its own chip selection signal but at one time, only one bank can be accessed. The EXMC support code execution from external memory. The EXMC also can be configured to interface with the most common LCD module of Motorola 6800 and Intel 8080 series and reduce the system cost and complexity.

3.19. Debug mode

■ Serial wire JTAG debug port (SWJ-DP)

The ARM®SWJ-DP Interface is embedded and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

3.20. Package and operation temperature

■ LQFP100 (GD32E103Vx), LQFP64 (GD32E103Rx) and LQFP48 (GD32E103Cx) QFN36



(GD32E103Tx)

■ Operation temperature range: -40°C to +85°C (industrial level)



4. Electrical characteristics

4.1. Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings(1)(4)

Symbol	Parameter	Min	Max	Unit
V_{DD}	External voltage range ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	٧
V_{DDA}	External analog supply voltage	V _{SSA} - 0.3	V _{SSA} + 3.6	V
V _{BAT}	External battery supply voltage	V _{SS} - 0.3	V _{SS} + 3.6	V
VIN	Input voltage on 5V tolerant pin ⁽³⁾	V _{SS} - 0.3	$V_{DD} + 3.6$	٧
VIN	Input voltage on other I/O	V _{SS} - 0.3	3.6	٧
$ \Delta V_{DDX} $	Variations between different V _{DD} power pins		50	mV
Vssx -Vss	Variations between different ground pins	_	50	mV
lio	Maximum current for GPIO pins	rrent for GPIO pins —		mA
TA	Operating temperature range	-40	+85	ပ္
	Power dissipation at T _A = 85°C of LQFP100	_	813	
P _D	Power dissipation at T _A = 85°C of LQFP64	_	733	mW
FD	Power dissipation at T _A = 85°C of LQFP48	_	574	IIIVV
	Power dissipation at T _A = 85°C of QFN36	_	1086	
T _{STG}	Storage temperature range	-55	+150	°C
TJ	Maximum junction temperature	_	125	ç

⁽¹⁾ Guaranteed by design, not tested in production.

4.2. Operating conditions characteristics

Table 4-2. DC operating conditions

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V_{DD}	Supply voltage —		1.71	3.3	3.6	V
\/	Analog supply voltage ADC not used		1.71	3.3	3.6	\/
V _{DDA}	Analog supply voltage ADC used	_	2.4	3.3	3.6	V
V _{BAT}	Battery supply voltage	_	1.71	_	3.6	V

⁽¹⁾ Guaranteed by design, not tested in production.

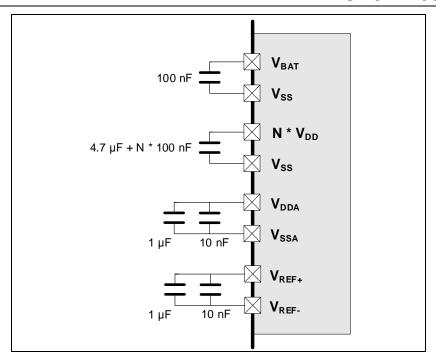
Figure 4-1. Recommended power supply decoupling capacitors⁽¹⁾ (2)

⁽²⁾ All main power and ground pins should be connected to an external power source within the allowable range.

⁽³⁾ V_{IN} maximum value cannot exceed 6.5 V.

⁽⁴⁾ It is recommended that V_{DD} and V_{DDA} are powered by the same source. The maximum difference between V_{DD} and V_{DDA} does not exceed 300 mV during power-up and operation.





- (1) The V_{REF+} and V_{REF-} pins are only available on no less than 100-pin packages, or else the V_{REF+} and V_{REF-} pins are not available and internally connected to V_{DDA} and V_{SSA} pins.
- (2) All decoupling capacitors need to be as close as possible to the pins on the PCB board.

Table 4-3. Clock frequency⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	AHB clock frequency	_	_	120	MHz
f _{APB1}	APB1 clock frequency	_	_	60	MHz
f _{APB2}	APB2 clock frequency	_	_	120	MHz

⁽¹⁾ Guaranteed by design, not tested in production.

Table 4-4. Operating conditions at Power up/ Power down⁽¹⁾

Symbol	Parameter	Parameter Conditions		Max	Unit
4	V _{DD} rise time rate		0	8	us/V
t∨DD	V _{DD} fall time rate	_	20	8	μ5/ ν

⁽¹⁾ Guaranteed by design, not tested in production.

Table 4-5. Start-up timings of Operating conditions(1)(2)(3)

Symbol	Parameter	Conditions	Тур	Unit
4	Start-up time	Clock source from HXTAL	468	
t _{start-up}	Start-up time	Clock source from IRC8M	86.8	μs

- (1) Based on characterization, not tested in production.
- (2) After power-up, the start-up time is the time between the rising edge of NRST high and the main function.
- (3) PLL is off.

Table 4-6. Power saving mode wakeup timings characteristics(1)(2)

Symbol	Parameter	Тур	Unit
tsleep	Wakeup from Sleep mode	4.3	
t _{Deep-sleep}	Wakeup from Deep-sleep mode (LDO On)	18.0	μs
	Wakeup from Deep-sleep mode (LDO in low power	18.0	



Symbol	Parameter	Тур	Unit
	mode)		
tStandby	Wakeup from Standby mode	82.0	

⁽¹⁾ Based on characterization, not tested in production.

4.3. Power consumption

The power measurements specified in the tables represent that code with data executing from on-chip Flash with the following specifications.

Table 4-7. Power consumption characteristics (2)(3)(4)(5)

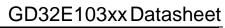
Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock=120 MHz, All peripherals enabled	_	28.1	_	mA
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz, System clock = 120 MHz, All peripherals disabled	_	16.0	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 108 MHz, All peripherals enabled	_	24.6	_	mA
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz, System clock = 108 MHz, All peripherals disabled	_	14.7	_	mA
les des	Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 96 MHz, All peripherals enabled	_	22.3	_	mA
IDD+IDDA	(Run mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 96 MHz, All peripherals disabled	_	13.6	_	mA
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz, System clock = 72 MHz, All peripherals enabled	_	17.2	_	mA
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz, System clock = 72 MHz, All peripherals disabled	_	10.8	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 48 MHz, All peripherals enabled	_	12.3	_	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 48 MHz, All peripherals disabled	_	8.1	_	mA

⁽²⁾ The wakeup time is measured from the wakeup event to the point at which the application code reads the first instruction under the below conditions: $V_{DD} = V_{DDA} = 3.3 \text{ V}$, IRC8M = System clock = 8 MHz.



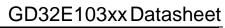
GD32E103xx Datasheet

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Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 36 MHz, All peripherals	_	9.8	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 36 MHz, All peripherals	_	6.7	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 24 MHz, All peripherals	_	7.4	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 24 MHz, All peripherals	_	5.3	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 16 MHz, All peripherals	_	5.7	_	mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 16 MHz, All peripherals	_	4.4	_	mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 8 MHz, All peripherals	_	4.1	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 8 MHz, All peripherals	_	3.4	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
		System clock = 4 MHz, All peripherals	_	1.3	_	mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 4 MHz,				
		System clock = 4 MHz, All peripherals	_	1.0	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 2 \text{ MHz,}$				
		System clock = 2 MHz, All peripherals	_	0.9	_	mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 2 MHz,				
		System Clock = 2 MHz, All peripherals	_	0.7	_	mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 120 MHz, CPU clock off, All	_	20.5	_	mA
	Supply current	peripherals enabled				
	(Sleep mode)	V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 120 MHz, CPU clock off, All	_	6.9	_	mA
		peripherals disabled				
1		1 1			ii	





		GD32L	100		atuo	100	
Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit	
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					
		System Clock = 108 MHz, CPU clock off, All	_	18.6	_	mΑ	
		peripherals enabled					
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					l
		System Clock = 108 MHz, CPU clock off, All	_	6.4	_	mΑ	ì
		peripherals disabled					
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 96 MHz, CPU clock off, All	_	16.5	_	mΑ	ì
		peripherals enabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$					ì
		System Clock = 96 MHz, CPU clock off, All	_	5.8	_	mA	ı
		peripherals disabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$					ì
		System Clock = 72 MHz, CPU clock off, All	_	13	_	mΑ	ì
		peripherals enabled					ì
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 72 MHz, CPU clock off, All	_	5	_	mΑ	ì
		peripherals disabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 48 MHz, CPU clock off, All	_	9.5	_	mΑ	ı
		peripherals enabled					ì
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 48 MHz, CPU clock off, All	_	4.1		mA	ı
		peripherals disabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ı
		System Clock = 36 MHz, CPU clock off, All	_	7.7	_	mA	ì
		peripherals enabled					ì
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$					ı
		System Clock = 36 MHz, CPU clock off, All	_	3.7		mA	ı
		peripherals disabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 24 MHz, CPU clock off, All	_	5.9	_	mA	ì
		peripherals enabled					ı
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$					ı
		System Clock = 24 MHz, CPU clock off, All	_	3.3	_	mA	ı
		peripherals disabled					ì
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 16 MHz, CPU clock off, All	_	4.8	_	mA	ì
		peripherals enabled					1
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					ì
		System Clock = 16 MHz, CPU clock off, All	_	3	_	mA	ì
		peripherals disabled					ı





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Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 8 MHz, CPU clock off, All	_	3.6	_	mΑ
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System Clock = 8 MHz, CPU clock off, All	_	2.7	_	mΑ
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 4 \text{ MHz},$				
		System Clock = 4 MHz, CPU clock off, All	_	1.1	_	mΑ
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 4 \text{ MHz},$				
		System Clock = 4 MHz, CPU clock off, All	_	0.6	_	mΑ
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 2 \text{ MHz},$				
		System Clock = 2 MHz, CPU clock off, All	_	0.8	_	mΑ
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 2 \text{ MHz},$				
		System Clock = 2 MHz, CPU clock off, All	_	0.6	_	mΑ
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in run mode,}$				
	Supply current	IRC40K off, RTC off, All GPIOs analog	_	41.8	550	μΑ
	(Deep-Sleep	mode				
	mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V}$, LDO in low power				
	111000)	mode, IRC40K off, RTC off, All GPIOs	_	31.8	550	μA
		analog mode				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K on,}$		2.1	11	
		RTC on		2.1	"	μA
	Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K on,}$				
	(Standby	RTC off	_	2.0	11	μΑ
	mode)					
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K off,}$	_	1.5	11	μΑ
		RTC off				
		V_{DD} off, V_{DDA} off, $V_{BAT} = 3.6 \text{ V}$, LXTAL on				
		with external crystal, RTC on, LXTAL High	_	1.6	_	μΑ
		driving				
		V_{DD} off, V_{DDA} off, $V_{BAT} = 3.3 \text{ V}$, LXTAL on				
Battery supply	with external crystal, RTC on, LXTAL High	_	1.4	_	μΑ	
I _{BAT}		driving				
mode)	V_{DD} off, V_{DDA} off, $V_{BAT} = 2.5 \text{ V}$, LXTAL on					
	with external crystal, RTC on, LXTAL High	_	1.3	_	μΑ	
	driving					
		V_{DD} off, V_{DDA} off, $V_{BAT} = 1.71 \text{ V}$, LXTAL on				
l v	with external crystal, RTC on, LXTAL High	_	1.2	_	μΑ	
		driving				



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Vob off, Voba off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vob off, Voba off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vob off, Voba off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vob off, Voba off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vob off, Voba off, Veat = 3.7 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vob off, Voba off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vob off, Voba off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vob off, Voba off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vob off, Voba off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vob off, Voba off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low On On With external crystal, RTC on, LXTAL Low On On With external crystal, RTC on, LXTAL Low On On With external crystal, RTC on, LXTAL Low On On With external crystal, RTC on, LXTAL Low On On With external crystal, RTC on, LXTAL Low On	0	5	ODSZL		1		
with external crystal, RTC on, LXTAL Medium High driving	Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
Medium High driving Vod off, Voda off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vod off, Voda off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vod off, Voda off, Veat = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vod off, Voda off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving Vod off, Voda off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vod off, Voda off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vod off, Voda off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vod off, Voda off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vod off, Voda off, Veat = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving Vod off, Voda off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving Vod off, Voda off, Veat = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving Vod off, Voda off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving Vod off, Voda off, Veat = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low On with external crystal, RTC on, LXTAL Low On on with external crystal, RTC on, LXTAL Low On on with external crystal, RTC on, LXTAL Low On on with external crystal, RTC on, LXTAL Low On on with external crystal, RTC on, LXTAL Low On							
Vod off, Voda off, Veat = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL			-		1.3	_	μA
with external crystal, RTC on, LXTAL			Medium High driving				
Medium High driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μA Medium High driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium High driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μA Medium Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA							
V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μA Medium High driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium High driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL 0 — 0.9 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL 0 — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL 0 — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA			with external crystal, RTC on, LXTAL	_	1.1	_	μΑ
with external crystal, RTC on, LXTAL — 1.0 — μA Medium High driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium High driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μA Medium Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA			Medium High driving				
Medium High driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low driving			V_{DD} off, V_{DDA} off, $V_{BAT} = 2.5 \text{ V}$, LXTAL on				
VDD OFF, VDDA OFF, VBAT = 1.71 V, LXTAL ON with external crystal, RTC on, LXTAL Medium High driving VDD OFF, VDDA OFF, VBAT = 3.6 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD OFF, VDDA OFF, VBAT = 3.3 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD OFF, VDDA OFF, VBAT = 3.3 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD OFF, VDDA OFF, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD OFF, VDDA OFF, VBAT = 1.71 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD OFF, VDDA OFF, VBAT = 3.6 V, LXTAL ON with external crystal, RTC on, LXTAL ON with external crystal, RTC on, LXTAL ON with external crystal, RTC on, LXTAL ON driving VDD OFF, VDDA OFF, VBAT = 3.3 V, LXTAL ON with external crystal, RTC on, LXTAL Low driving VDD OFF, VDDA OFF, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Low driving VDD OFF, VDDA OFF, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Low driving VDD OFF, VDDA OFF, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Low On			with external crystal, RTC on, LXTAL	_	1.0	_	μA
with external crystal, RTC on, LXTAL — 0.9 — μΑ Medium High driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL — 1.0 — μΑ Medium Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μΑ Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μΑ Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μΑ Medium Low driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μΑ driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μΑ			Medium High driving				
Medium High driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low D 0.6 — µA			V_{DD} off, V_{DDA} off, $V_{BAT} = 1.71 \text{ V}$, LXTAL on				
VDD Off, VDDA Off, VBAT = 3.6 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD Off, VDDA Off, VBAT = 3.3 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD Off, VDDA Off, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Medium Low driving VDD Off, VDDA Off, VBAT = 1.71 V, LXTAL ON with external crystal, RTC on, LXTAL Low Offiving VDD Off, VDDA Off, VBAT = 3.3 V, LXTAL ON with external crystal, RTC on, LXTAL Low Offiving VDD Off, VDDA Off, VBAT = 2.5 V, LXTAL ON with external crystal, RTC on, LXTAL Low Offiving VDD Off, VDDA Off, VBAT = 1.71 V, LXTAL ON With external crystal, RTC on, LXTAL Low Offiving VDD Off, VDDA Off, VBAT = 1.71 V, LXTAL ON With external crystal, RTC on, LXTAL Low Offiving			with external crystal, RTC on, LXTAL	_	0.9	_	μΑ
with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low driving			Medium High driving				
Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL bow — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL	_	1.0	_	μΑ
with external crystal, RTC on, LXTAL — 0.9 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL bow driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA			Medium Low driving				
Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving			V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL	_	0.9	_	μΑ
with external crystal, RTC on, LXTAL — 0.7 — μA Medium Low driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving VDD off, VDDA off, VBAT = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving VDD off, VDDA off, VBAT = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving VDD off, VDDA off, VBAT = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving VDD off, VDDA off, VBAT = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			Medium Low driving				
Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V_{DD} off, V_{DDA} off, $V_{BAT} = 2.5 \text{ V}$, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL	_	0.7	_	μA
with external crystal, RTC on, LXTAL — 0.6 — μA Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			Medium Low driving				
Medium Low driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V_{DD} off, V_{DDA} off, $V_{BAT} = 1.71$ V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL		0.6	_	μΑ
with external crystal, RTC on, LXTAL Low — 0.9 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			Medium Low driving				
driving V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL Low	_	0.9	_	μΑ
with external crystal, RTC on, LXTAL Low — 0.8 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			driving				
driving V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL Low	_	8.0	_	μΑ
with external crystal, RTC on, LXTAL Low — 0.6 — μA driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			driving				
driving V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			V_{DD} off, V_{DDA} off, $V_{BAT} = 2.5$ V, LXTAL on				
V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Low — 0.5 — μA			with external crystal, RTC on, LXTAL Low	_	0.6	_	μΑ
with external crystal, RTC on, LXTAL Low — 0.5 — μA			driving				
			V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on				
drivina			with external crystal, RTC on, LXTAL Low	_	0.5	_	μΑ
<u> </u>			driving				

- (1) Based on characterization, not tested in production.
- (2) Unless otherwise specified, all values given for T_A = 25 $\,^{\circ}\mathbb{C}$ and test result is mean value.
- (3) When System Clock is less than 4 MHz, an external source is used, and the HXTAL bypass function is needed, no PLL.
- (4) When System Clock is greater than 8 MHz, a crystal 25 MHz is used, and the HXTAL bypass function is closed, using PLL.
- (5) When analog peripheral blocks such as ADCs, DACs, HXTAL, LXTAL, IRC8M, or IRC40K are ON, an additional power consumption should be considered.



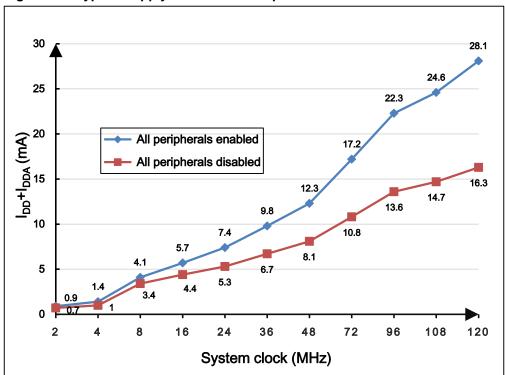


Figure 4-2. Typical supply current consumption in Run mode



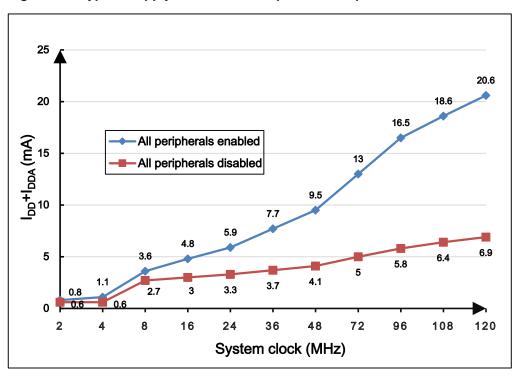


Table 4-8. Peripheral current consumption characteristics⁽¹⁾

		•		
	Peripherials ⁽⁴⁾		Typical consumption at 25 ℃ (TYP)	Unit
APB1	DAC ⁽²⁾		0.44	mΑ





GD3ZE 103XX DalaSi				
	Peripherials ⁽⁴⁾	Typical consumption at 25 °C (TYP)	Unit	
	PMU	0.18		
	ВКРІ	0.38		
	CAN1	0.3		
	CAN0	0.32		
	I2C1	0.77		
	I2C0	0.77		
	UART4	0.78		
	UART3	0.78		
	USART2	0.78		
	USART1	0.78		
	SPI2	0.72		
_	SPI1	0.78		
_	WWDGT	0.03		
	TIMER13	0.32		
	TIMER12	0.3		
_	TIMER11	0.31		
_	TIMER6	0.05		
_	TIMER5	0.04		
_	TIMER4	0.38		
_	TIMER3	0.37		
_	TIMER2	0.36		
_	TIMER1	0.37		
ADDAPB1	CTC	0.68		
7.007.11	TIMER10	0.56		
	TIMER9	0.58		
_		0.6	1	
_	TIMER8	0.52	1	
_	USART0		<u> </u> 	
_	TIMER7	0.87		
_	SPI0	0.09	_	
4.000	TIMER0	0.65	<u> </u> 	
APB2	ADC1 ⁽³⁾	1.36	<u> </u> 	
_	ADC0 ⁽³⁾	1.35	_	
_	GPIOE	0.18	1	
	GPIOD	0.19		
	GPIOC	0.2		
_	GPIOB	0.18		
_	GPIOA	0.19		
	GPIOF	0.04		
	USBFS	1.48		
AHB	EXMC	0.29		
	CRC	0.03		



Peripherials ⁽⁴⁾		Typical consumption at 25 °C (TYP)	Unit
	DMA1	0.31	
	DMA0	0.39	

- (1) Based on characterization, not tested in production.
- (2) DEN0 and DEN1 bits in the DAC_CTL register are set to 1, and the converted value set to 0x800.
- (3) System clock = f_{HCLK} = 72 MHz, f_{APB1} = f_{HCLK}/2, f_{APB2} = f_{HCLK}, f_{ADCCLK} = f_{APB2}/2, ADCON bit is set to 1.
- (4) If there is no other description, then HXTAL = 25 MHz, system clock = f_{HCLK} = 120 MHz, f_{APB1} = $f_{HCLK}/2$, f_{APB2} = f_{HCLK} .

4.4. EMC characteristics

EMS (electromagnetic susceptibility) includes ESD (Electrostatic discharge, positive and negative) and FTB (Burst of Fast Transient voltage, positive and negative) testing result is given in the <u>Table 4-9. EMS characteristics</u>(1), based on the EMS levels and classes compliant with IEC 61000 series standard.

Table 4-9. EMS characteristics(1)

Symbol	Parameter	Conditions	Level/Class
	Voltage applied to all device pins to	$V_{DD} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C},$	
V _{ESD}	induce a functional disturbance	LQFP100, $f_{HCLK} = 120 \text{ MHz}$	3A
	induce a functional disturbance	conforms to IEC 61000-4-2	
	Fast transient voltage burst applied to	$V_{DD}= 3.3 \text{ V}, T_{A}= 25 ^{\circ}\text{C},$	
V_{FTB}	induce a functional disturbance through	gh LQFP100, f _{HCLK} = 120 MHz	
	100 pF on V_{DD} and V_{SS} pins	conforms to IEC 61000-4-4	

⁽¹⁾ Based on characterization, not tested in production.

4.5. Power supply supervisor characteristics

Table 4-10. Power supply supervisor characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
		LVDT<2:0> = 000(rising edge)	_	2.07	_		
		LVDT<2:0> = 000(falling edge)	_	1.97			
		LVDT<2:0> = 001(rising edge)	_	2.2			
		LVDT<2:0> = 001(falling edge)	_	2.1			
$V_{LVD}^{(1)}$	Low voltage Detector Threshold	LVDT<2:0> = 010(rising edge)	_	2.34		V	
		LVDT<2:0> = 010(falling edge)	_	2.24			
		LVDT<2:0> = 011(rising edge)	_	2.47			
		LVDT<2:0> = 011(falling edge)	_	2.37	_		
		LVDT<2:0> = 100(rising edge)	_	2.61	_		



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		LVDT<2:0> = 100(falling edge)	_	2.51	_	
		LVDT<2:0> = 101(rising edge)	_	2.74		
		LVDT<2:0> = 101(falling edge)	_	2.64	_	
		LVDT<2:0> = 110(rising edge)	_	2.88		
		LVDT<2:0> = 110(falling edge)		2.78		
		LVDT<2:0> = 111(rising edge)		3.01		
		LVDT<2:0> = 111(falling edge)	_	2.91		
V _{LVDhyst} ⁽²⁾	LVD hystersis	_	_	100	_	mV
V _{POR} ⁽¹⁾	Power on reset threshold		_	1.67		V
V _{PDR} ⁽¹⁾	Power down reset threshold	_	_	1.62	_	V
V _{PDRhyst} ⁽²⁾	PDR hysteresis		_	40	_	mV
trsttempo ⁽²⁾	Reset temporization		_	2	_	ms

⁽¹⁾ Based on characterization, not tested in production.

4.6. Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on the two measurement methods.

Table 4-11. ESD characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V	Electrostatic discharge	T _A = 25 °C; JESD22-	_		5000	V
VESD(HBM)	voltage (human body model)	A114			5000	V
V	Electrostatic discharge	T _A = 25 °C;			900	W
Vesd(cdm)	voltage (charge device model)	JESD22-C101			800	V

⁽¹⁾ Based on characterization, not tested in production.

⁽²⁾ Guaranteed by design, not tested in production.



Table 4-12. Static latch-up characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
LU	I-test	T _A = 25 °C; JESD78	_	_	±200	mA
LO	V _{supply} over voltage	TA = 25 C, JESD76	_	_	5.4	٧

⁽¹⁾ Based on characterization, not tested in production.

4.7. External clock characteristics

Table 4-13. High speed external clock (HXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HXTAL} ⁽¹⁾	Crystal or ceramic frequency	1.71 ≤ V _{DD} ≤ 3.6 V	4	8	32	MHz
R _F ⁽²⁾	Feedback resistor	V _{DD} = 3.3 V	_	400	_	kΩ
	Recommended matching					
CHXTAL ^{(2) (3)}	capacitance on OSCIN and	_	_	20	30	pF
	OSCOUT					
Ducy _(HXTAL) ⁽²⁾	Crystal or ceramic duty cycle	_	30	50	70	%
g _m ⁽²⁾	Oscillator transconductance	Startup	_	25	_	mA/V
IDD(HXTAL) (1)	Crystal or ceramic operating	V _{DD} = 3.3 V, T _A = 25 °C		1.1		mA
	current	VDD = 3.3 V, TA = 25 C		1.1		IIIA
tsuhxtal ⁽¹⁾	Crystal or ceramic startup time	V _{DD} = 3.3 V, T _A = 25 °C		1.8	_	ms

⁽¹⁾ Based on characterization, not tested in production.

Table 4-14. High speed external clock characteristics (HXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f (1)	External clock source or oscillator	V 2 2 V	1		50	MHz
f _{HXTAL_ext} ⁽¹⁾	frequency	$V_{DD} = 3.3 \text{ V}$	'		50	IVIITZ
V _{HXTALH} ⁽²⁾	OSCIN input pin high level voltage	V _{DD} = 3.3 V	0.7 V _{DD}	_	V_{DD}	V
V _{HXTALL} ⁽²⁾	OSCIN input pin low level voltage	VDD = 3.3 V	Vss	_	$0.3~V_{DD}$	V
t _{H/L(HXTAL)} (2)	OSCIN high or low time	_	5	_	_	ns
t _{R/F(HXTAL)} (2)	OSCIN rise or fall time	_	_	_	10	ns
C _{IN} ⁽²⁾	OSCIN input capacitance	_	_	5	_	pF
Ducy _(HXTAL) (2)	Duty cycle	_	40	_	60	%

⁽¹⁾ Based on characterization, not tested in production.

⁽²⁾ Guaranteed by design, not tested in production.

⁽³⁾ $C_{HXTAL1} = C_{HXTAL2} = 2^*(C_{LOAD} - C_S)$, For C_{HXTAL1} and C_{HXTAL2} , it is recommended matching capacitance on OSCIN and OSCOUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance.

⁽²⁾ Guaranteed by design, not tested in production.



Table 4-15. Low speed external clock (LXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL} ⁽¹⁾	Crystal or ceramic frequency	V _{DD} = 3.3 V	_	32.768	_	kHz
C _{LXTAL} ⁽²⁾ (3)	Recommended matching capacitance on OSC32IN and OSC32OUT	_	_	10	_	pF
Ducy _(LXTAL) (2)	Crystal or ceramic duty cycle	_	30	_	70	%
		Lower driving capability	ı	4		
~ (2)	Oscillator	Medium low driving capability	-	6	-	/
gm ⁽²⁾	transconductance	Medium high driving capability	1	12	l	μA/V
		Higher driving capability		18		
		Lower driving capability		0.7		
. (1)	Crystal or ceramic	Medium low driving capability	1	0.8	1	
I _{DDLXTAL} ⁽¹⁾	operating current	Medium high driving capability	1	1.1	1	μΑ
		Higher driving capability	_	1.4	_	
tsulxtal ^{(1) (4)}	Crystal or ceramic startup time	_	_	1.8	_	s

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3) $C_{LXTAL1} = C_{LXTAL2} = 2*(C_{LOAD} C_S)$, For C_{LXTAL1} and C_{LXTAL2} , it is recommended matching capacitance on OSC32IN and OSC32OUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance.
- (4) tsulxtal is the startup time measured from the moment it is enabled (by software) to the 32.768 kHz oscillator stabilization flags is SET. This value varies significantly with the crystal manufacturer.

Table 4-16.Low speed external user clock characteristics (LXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL_ext} ⁽¹⁾	External clock source or oscillator frequency	V _{DD} = 3.3 V	_	32.768	1000	kHz
V _{LXTALH} ⁽²⁾	OSC32IN input pin high level voltage	_	0.7 V _{DD}	l	V_{DD}	V
V _{LXTALL} ⁽²⁾	OSC32IN input pin low level voltage	_	Vss	l	0.3 V _{DD}	V
t _{H/L(LXTAL)} (2)	OSC32IN high or low time	_	450		_	
t _{R/F(LXTAL)} (2)	OSC32IN rise or fall time	_		_	50	ns
C _{IN} ⁽²⁾	OSC32IN input capacitance	_	_	5	_	pF
Ducy _(LXTAL) (2)	Duty cycle	_	30	50	70	%

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.



4.8. Internal clock characteristics

Table 4-17. High speed internal clock (IRC8M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
firc8M	High Speed Internal Oscillator (IRC8M) frequency	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	_	8		MH z
	IDCOM accillator Fraguency	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 \text{ °C} \sim +85 \text{ °C}^{(1)}$	-2.5		+2.5	%
ACC:====	IRC8M oscillator Frequency – accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = 0 \text{ °C} \sim +85 \text{ °C}^{(1)}$	-1.8		+1.8	%
ACC _{IRC8M}		V _{DD} = V _{DDA} = 3.3 V, T _A = 25 °C	-1.0	_	+1.0	%
	IRC8M oscillator Frequency accuracy, User trimming step ⁽¹⁾	_	_	0.3		%
Ducyirc8m ⁽²⁾	IRC8M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDAIRC8M ⁽¹⁾	IRC8M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{IRC8M} = 8 \text{ MHz}$	_	110	_	μA
t _{SUIRC8M} ⁽¹⁾	IRC8M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{IRC8M} = 8 \text{ MHz}$	_	2		μs

⁽¹⁾ Based on characterization, not tested in production.

Table 4-18. Low speed internal clock (IRC40K) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
firc40K ⁽¹⁾	Low Speed Internal oscillator	$V_{DD} = V_{DDA} = 3.3 \text{ V},$	28	40	60	kHz
	(IRC40K) frequency	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}$	20	40	60	KHZ
(2)	IRC40K oscillator operating	V _{DD} = V _{DDA} = 3.3 V, T _A = 25 °C		0.42		
IDDAIRC40K ⁽²⁾	current			0.42	_	μA
tsuirc40K ⁽²⁾	IRC40K oscillator startup	\/ \/ 2 2 \/ T 25 °C		110		
	time	$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$		110		μs

⁽¹⁾ Guaranteed by design, not tested in production.

⁽²⁾ Guaranteed by design, not tested in production.

⁽²⁾ Based on characterization, not tested in production.



Table 4-19. High speed internal clock (IRC48M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	High Speed Internal					
f _{IRC48M}	Oscillator (IRC48M)	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	_	48	_	MHz
	frequency					
		$V_{DD} = V_{DDA} = 3.3 \text{ V},$	-4.0		5.0	%
	IDC49M cocillator Fraguency	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}^{(1)}$	-4.0		3.0	%
	IRC48M oscillator Frequency accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 V$,	2.0		3.0	%
ACC _{IRC48M}	_	$T_A = 0 {}^{\circ}\text{C} \sim +85 {}^{\circ}\text{C}^{(1)}$	-3.0	_	3.0	%
ACCIRC48M		$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	-2.0	_	2.0	%
	IRC48M oscillator Frequency					
	accuracy, User trimming	_	_	0.1	_	%
	step ⁽¹⁾					
Ducy _{IRC48M} ⁽²⁾	IRC48M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDIRC48M ⁽¹⁾	IRC48M oscillator operating	$V_{DD} = V_{DDA} = 3.3 \text{ V},$		270		
IDDIRC48M(**)	current	$f_{IRC48M} = 48 \text{ MHz}$		270	_	μΑ
tsuirc48M ⁽¹⁾	IRC48M oscillator startup	$V_{DD} = V_{DDA} = 3.3 \text{ V},$		2.5		
ISUIRC48M(*)	time	f _{IRC48M} = 48 MHz		2.5		μs

⁽¹⁾ Based on characterization, not tested in production.

4.9. PLL characteristics

Table 4-20. PLL characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN} (1)	PLL input clock frequency	_	1	8	25	MHz
f PLLOUT	PLL output clock frequency	_	16	_	120	MHz
fvco	VCO output frequency	_	32	_	240	MHz
t _{LOCK} (2)	PLL lock time	_	_	_	300	μs
I _{DDA} ⁽¹⁾	Current consumption on	VCO freq = 240 MHz		350		
IDDA' /	V _{DDA}	VCO 11eq = 240 W112		330		μΑ
	Cycle to cycle Jitter			46		
Jitter _{PLL} (1)(3)	(rms)	System clock		40		nc
Jitterpll(1)(3)	Cycle to cycle Jitter	System Clock		463		ps
	(peak to peak)			403		

⁽¹⁾ Based on characterization, not tested in production.

Table 4-21. PLL1/2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN} ⁽¹⁾	PLL input clock frequency	_	1	8	25	MHz
f _{PLLOUT}	PLL output clock frequency	_	16	_	120	MHz
f _{VCO}	VCO output frequency	_	32	_	240	MHz

⁽²⁾ Guaranteed by design, not tested in production.

⁽²⁾ Guaranteed by design, not tested in production.

⁽³⁾ Value given with main PLL running.

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t _{LOCK} (2)	PLL lock time	_		300	μs
I _{DDA} ⁽¹⁾	Current consumption on VDDA	VCO freq = 240 MHz	320		μΑ
Jitter _{PLL} ⁽¹⁾⁽³⁾	Cycle to cycle Jitter	Sustam alaak	46		ns
	Cycle to cycle Jitter (peak to peak)	System clock	463		ps

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3) Value given with main PLL running

4.10. Memory characteristics

Table 4-22. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PEcyc ⁽¹⁾	Number of guaranteed program /erase cycles before failure(Endurance)	T _A = -40 °C ~ +85 °C	100	Ī	_	kcycles
t _{RET} ⁽¹⁾	Data retention time	10k cycles at T _A = 85 °C	10		_	years
t _{PROG} (2)	Word ⁽³⁾ programming time	T _A = -40 °C ~ +85 °C	37		44	μs
terase(2)	Page erase time	T _A = -40 °C ~ +85 °C	3.2		4	ms
t _{MERASE} (2)	Mass erase time	T _A = -40 °C ~ +85 °C	8	_	10	ms

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3) Word is 32 bits or 64 bits depend on PGW bit in FMC_WS register.

4.11. NRST pin characteristics

Table 4-23. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage	402/42/	-0.5		$0.3~V_{DD}$	\ /
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$1.8 \text{ V} \leq \text{V}_{DD} = \text{V}_{DDA}$	$0.7 \ V_{DD}$	_	$V_{DD} + 0.45$	V
V _{hyst} ⁽¹⁾	Schmidt trigger Voltage hysteresis	≤ 3.6 V	_	460	_	mV
R _{pu} ⁽²⁾	Pull-up equivalent resistor	_		40	_	kΩ

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.



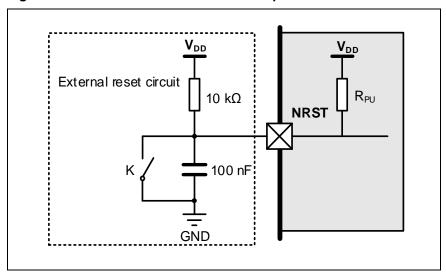


Figure 4-4. Recommended external NRST pin circuit

4.12. **GPIO** characteristics

Table 4-24. I/O port DC characteristics^{(1) (3)}

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V	Standard IO Low level input voltage	$1.8 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6$ V	_		0.3 V _{DD}	٧
V _{IL}	5V-tolerant IO Low level input voltage	$1.8 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6$ V	_	_	0.3 V _{DD}	V
	Standard IO High level input voltage	$1.8 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6$ V	0.7 V _{DD}	_	_	V
V _{IH}	5V-tolerant IO High level input voltage	$1.8 \text{ V} \le \text{V}_{DD} = \text{V}_{DDA} \le 3.6$ V	0.7 V _{DD}	_	_	٧
Vol		V _{DD} = 1.8 V	_	_	0.32	
	Low level output voltage	$V_{DD} = 2.5 \text{ V}$		_	0.24	V
	$(I_{IO} = +8 \text{ mA})$	$V_{DD} = 3.3 \text{ V}$	_	_	0.11	V
		$V_{DD} = 3.6 \text{ V}$	_	_	0.11	
		$V_{DD} = 1.8 \text{ V}$	_	_	0.53	
Vol	Low level output voltage	$V_{DD} = 2.5 \text{ V}$	_	_	0.60	V
VOL	$(I_{IO} = +20 \text{ mA})$	$V_{DD} = 3.3 \text{ V}$	_	_	0.28	V
		$V_{DD} = 3.6 \text{ V}$		_	0.27	
		$V_{DD} = 1.8 \text{ V}$	1.49	_	_	
Vон	High level output voltage	$V_{DD} = 2.5 \text{ V}$	2.27	_	_	V
VOH	$(I_{10} = +8 \text{ mA})$	$V_{DD} = 3.3 \text{ V}$	3.14	_	_	V
		$V_{DD} = 3.6 \text{ V}$	3.45	_	_	
	High level output voltage	$V_{DD} = 1.8 \text{ V}$	1.25	_	_	
Vон	(I _{IO} = +20 mA)	$V_{DD} = 2.5 \text{ V}$	1.89	_	_	V
	(110 – 720 1117)	$V_{DD} = 3.3 \text{ V}$	2.91	_	_	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{DD} = 3.6 V	3.23			
R _{PU} ⁽²⁾	Internal pull-up resistor	_	_	40	_	kΩ
R _{PD} ⁽²⁾	Internal pull-down resistor	_	_	40	_	kΩ

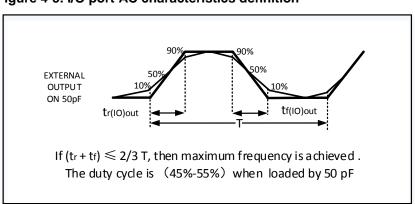
- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3) All pins except PC13 / PC14 / PC15. Since PC13 to PC15 are supplied through the Power Switch, which can only be obtained by a small current, the speed of GPIOs PC13 to PC15 should not exceed 2 MHz when they are in output mode(maximum load: 30 pF).

Table 4-25. I/O port AC characteristics(1)(2)

GPIOx_MDy[1:0] bit value ⁽³⁾	Parameter	Conditions	Max	Unit
CDIOv. CTL > MDv[1:0] = 10		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	9	
GPIOx_CTL->MDy[1:0] = 10 (IO_Speed = 2 MHz)	Maximum frequency(4)	$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	6	MHz
(10_opeed = 2 Wil 12)		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	4	
CDIOv. CTL > MDv[1:0] = 01		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	50	
GPIOx_CTL->MDy[1:0] = 01 (IO_Speed = 10 MHz)	Maximum frequency ⁽⁴⁾	$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	25	MHz
		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	15	
GPIOx_CTL->MDy[1:0] = 11		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	60	
(IO_Speed = 50 MHz)	Maximum frequency(4)	$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	30	MHz
(10_Speed = 30 Wi 12)		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	20	
GPIOx_CTL->MDy[1:0] = 11 and		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	70	
$GPIOx_SPDy = 1$	Maximum frequency(4)	$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	50	MHz
(IO_Speed = MAX)		$1.8 \le V_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	30	

- (1) Based on characterization, not tested in production.
- (3) The I/O speed is configured using the GPIOx_CTL -> MDy[1:0] bits. Refer to the GD32E103xx user manual which is selected to set the GPIO port output speed.
- (4) The maximum frequency is defined in Figure 4-5. I/O port AC characteristics definition.

Figure 4-5. I/O port AC characteristics definition





4.13. ADC characteristics

Table 4-26. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V _{DDA} ⁽¹⁾	Operating voltage	_	2.4	3.3	3.6	V	
V _{IN} ⁽¹⁾	ADC input voltage range	_	0	_	V _{REF+}	V	
f _{ADC} ⁽¹⁾	ADC clock	_	0.1	_	42	MHz	
		12-bit	0.007	_	3		
£ (1)	Sampling rate	10-bit	0.008	_	3.5	MCDC	
f _S ⁽¹⁾	Sampling rate	8-bit	0.01	_	4.2	MSPS	
		6-bit	0.011	_	5.25		
V _{AIN} ⁽¹⁾	Analog input voltage	16 external; 2 internal	0	_	V _{DDA}	V	
V _{REF+} (2)	Positive Reference Voltage	_	1.8	_	V _{DDA}	V	
V _{REF-} ⁽²⁾	Negative Reference Voltage	_	_	Vssa	_	V	
R _{AIN} ⁽²⁾	External input impedance	See Equation 1	_	_	24	kΩ	
R _{ADC} ⁽²⁾	Input sampling switch resistance	_	_	_	0.2	kΩ	
C _{ADC} ⁽²⁾	Input sampling capacitance	No pin/pad capacitance included	_	_	5.5	pF	
t _{CAL} ⁽²⁾	Calibration time	$f_{ADC} = 42 \text{ MHz}$	_	3.12	_	μs	
t _s (2)	Sampling time	$f_{ADC} = 42 \text{ MHz}$	0.036	_	5.7	μs	
	Total assurancian	12-bit	_	14	_		
4 (2)	Total conversion	10-bit	_	12	_	4/5	
tconv ⁽²⁾	time(including sampling time)	8-bit	_	10	_	1/ f _{ADC}	
	uille)	6-bit	_	8	_		
tsu ⁽²⁾	Startup time		_		1	μs	

⁽¹⁾ Based on characterization, not tested in production.

Equation 1: R_{AIN} max formula
$$R_{AIN} < \frac{T_s}{f_{ADC}*C_{ADC}*ln(2^{N+2})} - R_{ADC}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 4-27. ADC R_{AIN} max for f_{ADC} = 42 MHz

T _s (cycles)	ts(us)	R _{AINmax} (kΩ)
1.5	0.04	0.47
7.5	0.18	3.15
13.5	0.32	5.82
28.5	0.68	12.55
41.5	0.99	18.35
55.5	1.32	24.55
71.5	1.70	NA

⁽²⁾ Guaranteed by design, not tested in production.



T _s (cycles)	t _s (us)	R _{AINmax} (kΩ)
239.5	5.70	NA

Table 4-28. ADC dynamic accuracy at $f_{ADC} = 14 \text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 14 \text{ MHz}$	_	10.3		bits
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	_	63.8	_	
SNR	Signal-to-noise ratio	Input Frequency = 20	_	64.5	_	dB
THD	Total harmonic distortion	kHz		-67.5		uБ
1110	lotal narmonic distortion	Temperature = 25 °C		-07.3		

⁽¹⁾ Based on characterization, not tested in production.

Table 4-29. ADC dynamic accuracy at $f_{ADC} = 42 \text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
ENOB	Effective number of bits	f _{ADC} = 42 MHz		10.3	_	bits
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	_	63.8	_	
SNR	Signal-to-noise ratio	Input Frequency = 20 kHz	_	64.5	_	dB
THD	Total harmonic distortion	Temperature = 25 °C	l	-67.5		

⁽¹⁾ Based on characterization, not tested in production.

Table 4-30. ADC static accuracy at $f_{ADC} = 42 \text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Тур	Max	Unit
Offset	Offset error	f 40 MLI=	±1		
DNL	Differential linearity error	$f_{ADC} = 42 \text{ MHz}$	±1	_	LSB
INL	Integral linearity error	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	±3		

⁽¹⁾ Based on characterization, not tested in production.

4.14. Temperature sensor characteristics

Table 4-31. Temperature sensor characteristics(1)

Symbol	Parameter	Min	Тур	Max	Unit
TL	VSENSE linearity with temperature		±1.5	_	°C
Avg_Slope	Average slope	_	4.3	_	mV/°C
V ₂₅	Voltage at 25 °C	_	1.47	_	V
t start	Startup time	_	_	_	μs
t _{S_temp} (2)	ADC sampling time when reading the temperature	_	17.1	_	μs

⁽¹⁾ Based on characterization, not tested in production.

4.15. DAC characteristics

Table 4-32. DAC characteristics

⁽²⁾ Shortest sampling time can be determined in the application by multiple iterations.



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		OD32				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDA} ⁽¹⁾	Operating voltage	_	1.71	3.3	3.6	V
V _{REF+} ⁽¹⁾	Reference supply voltage	_	1.8	_	V_{DDA}	V
V _{REF-} ⁽¹⁾	Negative Reference			V _{SSA}		V
V REF-\ /	Voltage	_		VSSA		V
R _{LOAD} (2)	Load resistance	Resistive load with	5			kΩ
KLOAD(=/	Load resistance	buffer ON	5	_		K12
Ro ⁽²⁾	Impedance output with				15	۲0
KO(=)	buffer OFF	_	_	_	15	kΩ
C (2)	l and annaitance	No pin/pad capacitance				
C _{LOAD} ⁽²⁾	Load capacitance	included	_		50	pF
DAC_OUT	Lower DAC_OUT voltage		0.0			.,
min ⁽²⁾	with buffer ON	_	0.2	_		V
DAC_OUT	Higher DAC_OUT voltage				V _{DDA} -	.,
max ⁽²⁾	with buffer ON	_	_	_	0.2	V
DAC_OUT	Lower DAC_OUT voltage					
min ⁽²⁾	with buffer OFF	_	_	0.5		mV
DAC_OUT	Higher DAC_OUT voltage				V _{DDA} -	
max ⁽²⁾	with buffer OFF	_	_		1LSB	V
		With no load, middle				
(1)		code(0x800) on the input, V _{REF+}	_	380	_	μA
	DAC current consumption	= 3.6 V				•
I _{DDA} ⁽¹⁾	in quiescent mode	With no load, worst				
	iii quiossoiii iiisas	code(0xF1C) on the input, V _{REF+}	_	460	_	μA
		= 3.6 V				P
		With no load, middle				
		code(0x800) on the input, V _{REF+}	_	120	_	μA
	DAC current consumption	= 3.6 V				μ, τ
I _{DDVREF+} (1)	in quiescent mode	With no load, worst				
	in quioccon mode	code(0xF1C) on the input, V _{REF+}	_	320		μA
		= 3.6 V		020		μπ
	Differential non-linearity	- 3.0 V				
DNL ⁽¹⁾	error	DAC in 12-bit mode	_	_	±3	LSB
INL ⁽¹⁾	Integral non-linearity	DAC in 12-bit mode			±4	LSB
Offset ⁽¹⁾	Offset error	DAC in 12-bit mode			±12	LSB
GE ⁽¹⁾	Gain error	DAC in 12-bit mode			±0.5	%
T _{setting} (1)	Settling time	$C_{LOAD} \le 50 \text{ pF}, R_{LOAD} \ge 5 \text{ k}\Omega$		0.3	±0.5	
	Wakeup from off state	OLUAD < 50 pr, NLOAD > 5 KLZ		5		μs
T _{wakeup} ⁽²⁾	-	_	_	J	10	μs
Update	Max frequency for a correct				A	MC/-
rate(2)	DAC_OUT change from	$C_{LOAD} \le 50 \text{ pF}, R_{LOAD} \ge 5 \text{ k}\Omega$	_	_	4	MS/s
	code i to i±1LSBs					
PSRR ⁽²⁾	Power supply rejection	_	55	80	_	dB
	ratio					



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	(to V _{DDA})					

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.

4.16. I2C characteristics

Table 4-33. I2C characteristics(1)(2)

Symbol	Parameter	Conditions	Conditions mod		Fast mode		Fast mode plus		Unit
			Min	Max	Min	Max	Min	Max	
t _{SCL(H)}	SCL clock high time		4.0	_	0.6	_	0.2	_	μs
tscl(L)	SCL clock low time		4.7	_	1.3		0.5	_	μs
t _{su(SDA)}	SDA setup time	_	2	_	0.8	_	0.1	_	μs
th(SDA)	SDA data hold time		250	_	250		130	_	ns
tr(SDA/SCL)	SDA and SCL rise time	_	_	1000	20	300	_	120	ns
t _{f(SDA/SCL)}	SDA and SCL fall time	_	4	300	4	300	4	120	ns
t _{h(STA)}	Start condition hold time	_	4.0	_	0.6	_	0.26	_	μs

⁽¹⁾ Guaranteed by design, not tested in production

4.17. SPI characteristics

Table 4-34. Standard SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
f _{SCK}	SCK clock frequency	_	_	_	30	MHz		
tsck(H)	SCK clock high time	Master mode, $f_{PCLKx} = 120 \text{ MHz}$, presc = 8	31.83	33.33	34.83	ns		
tsck(L)	SCK clock low time	Master mode, f _{PCLKx} = 120 MHz, presc = 8	31.83	33.33	34.83	ns		
SPI master mode								
t _{V(MO)}	Data output valid time	_	_	7	_	ns		
t _{H(MO)}	Data output hold time	_	_	4	_	ns		
t _{SU(MI)}	Data input setup time	_	1	_	_	ns		
t _{H(MI)}	Data input hold time	_	0		_	ns		
		SPI slave mode						
tsu(NSS)	NSS enable setup time	_	0	_	_	ns		
t _{H(NSS)}	NSS enable hold time	_	1		_	ns		
t _{A(SO)}	Data output access time	_	_	9	_	ns		
t _{DIS(SO)}	Data output disable time	_	_	8	_	ns		

⁽²⁾ Test condition: GPIO_SPEED set 2 MHz and external pull-up resistor value is 1 k Ω when operate EEPROM with I2C.



t _{V(SO)}	Data output valid time	_		10	_	ns
t _{H(SO)}	Data output hold time	_	I	10	l	ns
t _{SU(SI)}	Data input setup time	_	0	_	_	ns
t _{H(SI)}	Data input hold time	_	2	_	_	ns

⁽¹⁾ Based on characterization, not tested in production.

4.18. I2S characteristics

Table 4-35. I2S characteristics^{(1) (2)}

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode (data: 16 bits,		2.070		
fск	Clock frequency	Audio frequency = 96 kHz)		3.078		MHz
		Slave mode	_	10	_	
t _H	Clock high time		_	162		ns
t∟	Clock low time	_	_	163	_	ns
tv(ws)	WS valid time	Master mode	_	2	_	ns
t _{H(WS)}	WS hold time	Master mode	_	2	_	ns
tsu(ws)	WS setup time	Slave mode	0	_	_	ns
t _{H(WS)}	WS hold time	Slave mode	3	_	_	ns
DuCyrono	I2S slave input clock duty	Slave mode		50		%
DuCy _(SCK)	cycle			30		%
t _{SU(SD_MR)}	Data input setup time	Master mode	0	_		ns
t _{su(SD_SR)}	Data input setup time	Slave mode	0	_		ns
t _{H(SD_MR)}	Data input hold time	Master receiver	1	_		ns
th(SD_SR)	Data input hold time	Slave receiver	3			ns
+ (05, 05)	Data output valid time	Slave transmitter		12		no
t _{v(SD_ST)}	Data output valid time	(after enable edge)	_	12		ns
4	Data autaut hald time	Slave transmitter		10		20
th(SD_ST)	Data output hold time	(after enable edge)		10		ns
t (05 :	Data output valid time	Master transmitter		10		ns
t _{v(SD_MT)}	Data output valid time	(after enable edge)	_	10		110
t. (00 14=	Data output hold time	Master transmitter		7		ne
th(SD_MT)	Data output hold time	(after enable edge)	_	′		ns

⁽¹⁾ Guaranteed by design, not tested in production.

4.19. USART characteristics

Table 4-36. USART characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{SCK}	SCK clock frequency	$f_{PCLKx} = 120 \text{ MHz}$	_	_	60	MHz
t _{SCK(H)}	SCK clock high time	f _{PCLKx} = 120 MHz	7.5	_	_	ns

⁽²⁾ Based on characterization, not tested in production.



tsck(L)	SCK clock low time	$f_{PCLKx} = 120 \text{ MHz}$	7.5	_	_	ns	
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⁽¹⁾ Guaranteed by design, not tested in production.

4.20. CAN characteristics

Refer to <u>Table 4-24. I/O port DC characteristics</u>(1) for more details on the input/output alternate function characteristics (CANTX and CANRX).

4.21. USBFS characteristics

Table 4-37. USBFS start up time

Symbol	Parameter	Max	Unit
tstartup ⁽¹⁾	USBFS startup time	1	μs

⁽¹⁾ Guaranteed by design, not tested in production.

Table 4-38. USBFS DC electrical characteristics

Symb	ol	Parameter	Conditions	Min	Тур	Max	Unit
	V_{DD}	USBFS operating voltage	_	3	_	3.6	
Input	V_{DI}	Differential input sensitivity	_	0.2	_	_	V
levels ⁽¹⁾	Vсм	Differential common mode range	Includes V _{DI} range	0.8	_	2.5	V
	V _{SE}	Single ended receiver threshold	_	1.3	_	2.0	
Output	V_{OL}	Static output level low	R_L of 1.0 $k\Omega$ to 3.6 V	_	0.064	0.3	V
levels (2)	V_{OH}	Static output level high	R_L of 15 $k\Omega$ to VSS	2.8	3.3	3.6	V
D (2	')	PA11, PA12(USB_DM/DP)	V V	17	20.574	24	
R _{PD} ⁽²⁾	.,	PA9(USB_VBUS)	$V_{IN} = V_{DD}$	0.65	_	2.0	kΩ
D(2	')	PA11, PA12(USB_DM/DP)	Mar. Mar.	1.5	1.585	2.1	V71
R _{PU} ⁽²	.,	PA9(USB_VBUS)	V _{IN} = V _{SS}	0.25	0.326	0.55	

⁽¹⁾ Guaranteed by design, not tested in production.

Table 4-39. USBFS electrical characteristics⁽¹⁾

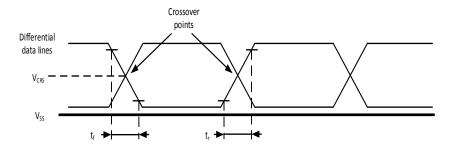
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _R	Rise time	$C_L = 50 pF$	4	ı	20	ns
t _F	Fall time	$C_L = 50 pF$	4	1	20	ns
t _{RFM}	Rise/fall time matching	t _R /t _F	90		110	%
V _{CRS}	Output signal crossover voltage	_	1.3	_	2.0	V

⁽¹⁾ Guaranteed by design, not tested in production.

Figure 4-6. USBFS timings: definition of data signal rise and fall time

⁽²⁾ Based on characterization, not tested in production.





4.22. EXMC characteristics

Table 4-40. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings(1)(2)(3)(4)

	-	•				
Symbol	Parameter	Min	Max	Unit		
t _{w(NE)}	EXMC_NE low time	40.5	42.5	ns		
tv(noe_ne)	EXMC_NEx low to EXMC_NOE low	0	_	ns		
t _{w(NOE)}	EXMC_NOE low time	40.5	42.5	ns		
th(NE_NOE)	EXMC_NOE high to EXMC_NE high hold time	0	_	ns		
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns		
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns		
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	32.2	_	ns		
t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	32.2	_	ns		
t _{h(DATA_NOE)}	Data hold time after EXMC_NOE high	0	_	ns		
t _{h(DATA_NE)}	Data hold time after EXMC_NEx high	0	_	ns		
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns		
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns		

⁽¹⁾ $C_L = 30 pF$.

Table 4-41. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	23.9	25.9	ns
t _{V(NWE_NE)}	EXMC_NEx low to EXMC_NWE low	7.3	_	ns
$t_{w(NWE)}$	EXMC_NWE low time	7.3	9.3	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3	9.3	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{V(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns
t. (40 NAD) 0	EXMC_AD(address) valid hold time after	15.6		20
th(AD_NADV)	EXMC_NADV high	15.0	_	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	_	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3	_	ns

⁽²⁾ Guaranteed by design, not tested in production.

⁽³⁾ Based on characterization, not tested in production.

⁽⁴⁾ Based on configure: f_{HCLK} = 120 MHz, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.



t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{v(DATA_NADV)}	EXMC_NADV high to DATA valid	0	_	ns
t _{h(DATA_NWE)}	Data hold time after EXMC_NWE high	7.3	_	ns

- (1) $C_L = 30 pF$.
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: f_{HCLK} = 120 MHz, AddressSetupTime = 0, AddressHoldTime= 1, DataSetupTime = 1.

Table 4-42. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	57.1	59.1	ns
tv(noe_ne)	EXMC_NEx low to EXMC_NOE low	23.9	_	ns
tw(NOE)	EXMC_NOE low time	32.2	34.2	ns
th(NE_NOE)	EXMC_NOE high to EXMC_NE high hold time	0	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{v(A_NOE)}	Address hold time after EXMC_NOE high	0	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
th(BL_NOE)	EXMC_BL hold time after EXMC_NOE high	0	_	ns
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	33.2	_	ns
t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	33.2	_	ns
t _{h(DATA_NOE)}	Data hold time after EXMC_NOE high	0	_	ns
t _{h(DATA_NE)}	Data hold time after EXMC_NEx high	0	_	ns
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns
T _{h(AD_NADV)}	EXMC_AD(adress) valid hold time after EXMC_NADV high	7.3	9.3	ns

- (1) $C_L = 30 \text{ pF}.$
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- $(4) \quad \text{Based on configure: } f_{\text{HCLK}} = 120 \text{ MHz, AddressSetupTime} = 0, \text{AddressHoldTime} = 1, \text{DataSetupTime} = 1.$

Table 4-43. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	40.5	42.5	ns
tv(nwe_ne)	EXMC_NEx low to EXMC_NWE low	7.3	_	ns
t _{w(NWE)}	EXMC_NWE low time	23.9	25.9	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
tv(nadv_ne)	EXMC_NEx low to EXMC_NADV low	0	_	ns
tw(NADV)	EXMC_NADV low time	7.3	9.3	ns
th(AD_NADV)	EXMC_AD(address) valid hold time after EXMC_NADV high	7.3	_	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	_	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns

t _{v(DATA_NADV)}	EXMC_NADV high to DATA valid	7.3	ns
th(DATA_NWE)	Data hold time after EXMC_NWE high	7.3	ns

- (1) $C_L = 30 pF$.
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: f_{HCLK} = 120 MHz, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime =1.

Table 4-44. Synchronous multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
tw(CLK)	EXMC_CLK period	33.2	_	ns
t _d (CLKL-NExL)	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	_	ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NADV low	0	_	ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	_	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	_	ns
td(CLKH-AIV)	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
td(CLKL-NOEL)	EXMC_CLK low to EXMC_NOE low	0	_	ns
t _{d(CLKH-NOEH)}	EXMC_CLK high to EXMC_NOE high	15.6	_	ns
td(CLKL-ADV)	EXMC_CLK low to EXMC_AD valid	0	_	ns
t _d (CLKL-ADIV)	EXMC_CLK low to EXMC_AD invalid	0	_	ns

- (1) $C_L = 30 pF$.
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: $f_{HCLK} = 120$ MHz, BurstAccessMode = Enable; Memory Type = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); Data Latency = 1.

Table 4-45. Synchronous multiplexed PSRAM write timings(1)(2)(3)(4)

Symbol Parameter		Min	Max	Unit
Symbol	Parameter	IVIIN	iviax	Unit
tw(CLK)	EXMC_CLK period	33.2		ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	ı	ns
td(CLKH-NExH)	EXMC_CLK high to EXMC_NEx high	15.6	ı	ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0	ı	ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	1	ns
td(CLKL-AV)	EXMC_CLK low to EXMC_Ax valid	0	_	ns
td(CLKH-AIV)	EXMC_CLK high to EXMC_Ax invalid	15.6	ı	ns
td(CLKL-NWEL)	EXMC_CLK low to EXMC_NWE low	0	ı	ns
t _{d(CLKH-NWEH)}	EXMC_CLK high to EXMC_NWE high	15.6	ı	ns
td(CLKL-ADIV)	EXMC_CLK low to EXMC_AD invalid	0		ns
t _{d(CLKL-DATA)}	EXMC_A/D valid data after EXMC_CLK low	0		ns
t _{h(CLKL-NBLH)}	EXMC_CLK low to EXMC_NBL high	0		ns
·	· · · · · · · · · · · · · · · · · · ·			

- (1) $C_L = 30 pF$.
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: $f_{HCLK} = 120$ MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); DataLatency = 1.

Table 4-46. Synchronous non-multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

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Symbol	Parameter	Min	Max	Unit
tw(CLK)	EXMC_CLK period	33.2		ns
td(CLKL-NExL)	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	_	ns
t _{d(CLKL-NADVL)}	EXMC_CLK low to EXMC_NADV low	0	_	ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NADV high	0	_	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
t _{d(CLKL-NOEL)}	EXMC_CLK low to EXMC_NOE low	0	_	ns
td(CLKH-NOEH)	EXMC_CLK high to EXMC_NOE high	15.6	_	ns

- (1) $C_L = 30 pF$.
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: f_{HCLK} = 120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC_CLK is 4 divided by HCLK); DataLatency = 1.

Table 4-47. Synchronous non-multiplexed PSRAM write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2	1	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	1	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	ı	ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0	ı	ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	ı	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	ı	ns
td(CLKH-AIV)	EXMC_CLK high to EXMC_Ax invalid	15.6	ı	ns
td(CLKL-NWEL)	EXMC_CLK low to EXMC_NWE low	0	ı	ns
t _{d(CLKH-NWEH)}	EXMC_CLK high to EXMC_NWE high	15.6	ı	ns
t _{d(CLKL-DATA)}	EXMC_A/D valid data after EXMC_CLK low	0		ns
th(CLKL-NBLH)	EXMC_CLK low to EXMC_NBL high	0	_	ns

- (1) $C_L = 30 \text{ pF}.$
- (2) Guaranteed by design, not tested in production.
- (3) Based on characterization, not tested in production.
- (4) Based on configure: f_{HCLK} = 120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3(EXMC_CLK is 4 divided by HCLK); DataLatency = 1.

4.23. TIMER characteristics

Table 4-48. TIMER characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t _{res} Timer resolution time			1	1	timerxclk
		ftimerxclk = 120 MHz	8.4	_	ns
f _{EXT}	Timer external clock	_	0	f _{TIMERxCLk} /2	MHz
IEXI	frequency	ftimerxclk = 120 MHz	0	60	MHz
RES	ES Timer resolution —		_	16	bit
tcounter	16-bit counter clock period	_	1	65536	timerxclk



	when internal clock is selected	f _{TIMERxCLK} = 120 MHz	0.0084	546	μs
4	Maximum passible sount	_	_	65536x65536	ttimerxclk
t _{MAX_COUNT}	Maximum possible count	ftimerxclk = 120 MHz	_	35.7	S

⁽¹⁾ Guaranteed by design, not tested in production.

4.24. WDGT characteristics

Table 4-49. FWDGT min/max timeout period at 40 kHz (IRC40K)(1)

Prescaler divider	PR[2:0] bits	Min timeout RLD[11:0] = 0x000	Max timeout RLD[11:0] = 0xFFF	Unit
1/4	000	0.1	409.6	
1/8	001	0.2	819.2	
1/16	010	0.4	1638.4	
1/32	011	0.8	3276.8	ms
1/64	100	1.6	6553.6	
1/128	101	3.2	13107.2	
1/256	110 or 111	6.4	26214.4	

⁽¹⁾ Guaranteed by design, not tested in production.

Table 4-50. WWDGT min-max timeout value at 60 MHz (f_{PCLK1})⁽¹⁾

· data · col · · · · · · · · · · · · · · · · · · ·						
Prescaler divider	PSC[2:0]	Min timeout value CNT[6:0] = 0x40	Unit	Max timeout value CNT[6:0] = 0x7F	Unit	
1/1	00	68.27		4.37		
1/2	01	136.53		8.74		
1/4	10	273.07	μs	17.48	ms	
1/8	11	546.13		34.96		

⁽¹⁾ Guaranteed by design, not tested in production.

4.25. Parameter conditions

Unless otherwise specified, all values given for $V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 \text{ }^{\circ}\text{C}.$



5. Package information

5.1. LQFP100 package outline dimensions

Figure 5-1. LQFP100 package outline

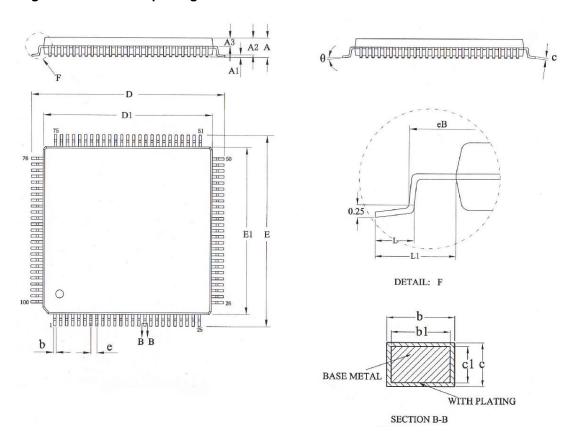


Table 5-1. LQFP100 package dimensions

Symbol	Min	Тур	Max
А	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
D	15.80	16.0	16.20
D1	13.90	14.0	14.10
E	15.80	16.0	16.20
E1	13.90	14.0	14.10
θ	0°	3.5°	7°
С	0.13	_	0.17
c1	0.12	0.13	0.14
L	0.45	0.6	0.75
L1	_	1.0REF	_



Symbol	Min	Тур	Max
b	0.18	0.20	0.26
b1	0.17	0.20	0.23
eB	15.05	_	15.35
е	_	0.50BSC	_

5.2. LQFP64 package outline dimensions

Figure 5-2. LQFP64 package outline

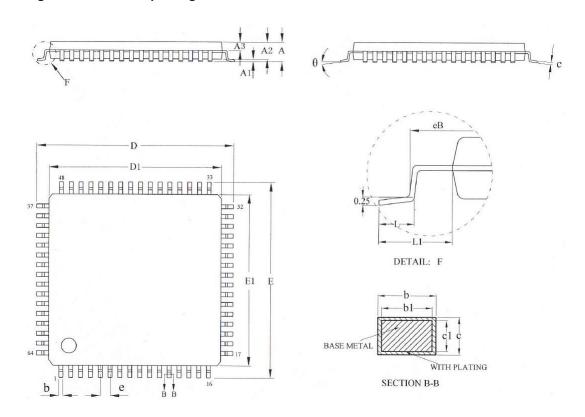


Table 5-2. LQFP64 package dimensions

Symbol	Min	Тур	Max
А	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
D	11.80	12.00	12.20
D1	9.90	10.00	10.10
Е	11.80	12.00	12.20
E1	9.90	10.00	10.10
θ	0°	3.5°	7°
С	0.13	_	0.17



Symbol	Min	Тур	Max
L	0.45	0.60	0.75
L1	_	1.00REF	_
b	0.17	0.20	0.27
е	_	0.50BSC	_
еВ	11.25	_	11.45

5.3. LQFP48 package outline dimensions

Figure 5-3. LQFP48 package outline

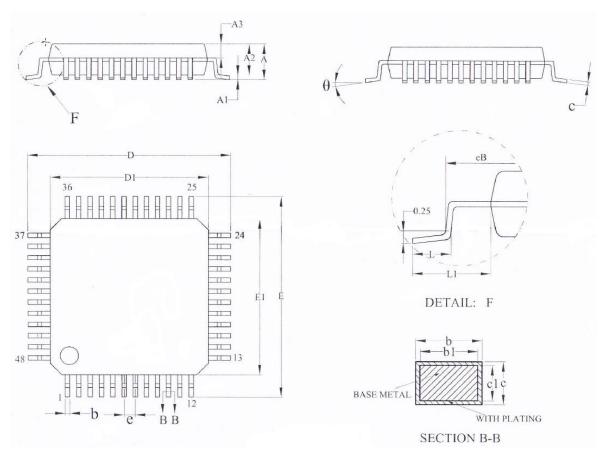


Table 5-3. LQFP48 package dimensions

Symbol	Min	Тур	Max
Α	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
А3	0.59	0.64	0.69
b	0.18	_	0.26
b1	0.17	0.20	0.23
С	0.13	_	0.17



c1	0.12	0.13	0.14
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
Е	8.80	9.00	9.20
eB	8.10	_	8.25
E1	6.90	7.00	7.10
е	0.50BSC		
L	0.45	_	0.75
L1	1.00REF		
θ	0	_	7°

5.4. QFN36 package outline dimensions

Figure 5-4. QFN36 package outline

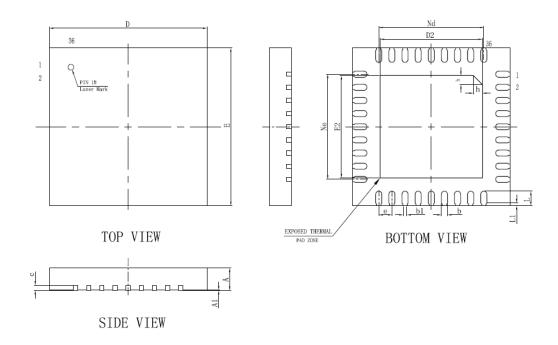




Table 5-4. QFN36 package dimensions

Symbol	Min	Тур	Max	
А	0.8	0.85	0.90	
A1	0.00	0.02	0.05	
b	0.18	0.23	0.30	
b1		0.16REF		
С	0.18	0.20	0.23	
D	5.90	6.00	6.10	
D2	3.80	3.90	4.00	
Nd	3.95	4.00	4.05	
е	0.50BSC			
E	5.90	6.00	6.10	
E2	3.80	3.90	4.00	
Ne	3.95	4.00	4.05	
L	0.50	0.55	0.60	
L1	0.10REF			
h	0.30	0.35	0.40	

Notes:

- 1. Formed lead shall be planar with respect to one another within 0.004 inches.
- 2. Both package length and width do not include mold flash and metal burr.

5.5. Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter " Θ ". For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

⊕ JA: Thermal resistance, junction-to-ambient.

 Θ JB: Thermal resistance, junction-to-board.

 Θ JC: Thermal resistance, junction-to-case.

 Ψ_{JB} : Thermal characterization parameter, junction-to-board.

 Ψ_{JT} : Thermal characterization parameter, junction-to-top center.

 Θ JA = (TJ - TA)/PD

 $\Theta_{JB} = (T_J - T_B)/P_D$

 $\Theta_{JC} = (T_J - T_C)/P_D$

Where, $T_J = Junction temperature$.

 T_A = Ambient temperature

T_B = Board temperature

T_C = Case temperature which is monitoring on package surface

P_D = Total power dissipation

⊕ JA represents the resistance of the heat flows from the heating junction to ambient air. It is



an indicator of package heat dissipation capability. Lower Θ JA can be considerate as better overall thermal performance. Θ JA is generally used to estimate junction temperature. Θ JB is used to measure the heat flow resistance between the chip surface and the PCB board. Θ JC represents the thermal resistance between the chip surface and the package top case. Θ JC is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 5-5. Package thermal characteristics(1)

Symbol	Condition	Package	Value	Unit
		LQFP100	49.18	
	T _A = 85°C, Natural convection, 2S2P	LQFP64	54.57	°C/W
⊕ JA	PCB	LQFP48	69.64	C/VV
		QFN36	36.82	
		LQFP100	22.70	
	T 25°C Cold plate 282B BCB	LQFP64	35.08	°C/W
⊕ JB	T _A = 25°C, Cold plate, 2S2P PCB	LQFP48	43.16	C/VV
		QFN36	9.79	
		LQFP100	12.52	
Θ	T _A = 25°C, Cold plate, 2S2P PCB	LQFP64	18.11	°C/W
⊕ 1C		LQFP48	25.36	C/VV
		QFN36	13.31	
		LQFP100	32.85	
Ψ_{JB}	$T_A = 85$ °C, Natural convection, 2S2P	LQFP64	35.41	°C/W
⊕ JB	PCB	LQFP48	47.75	C/VV
		QFN36	9.87	
Ψл		LQFP100	0.53	
	T _A = 85°C, Natural convection, 2S2P	LQFP64	1.10	°C/W
	PCB	LQFP48	2.45	J C/VV
		QFN36	0.43	

⁽¹⁾ Thermal characteristics are based on simulation, and meet JEDEC specification.

6. Ordering information

Table 6-1. Part ordering code for GD32E103xx devices

Ordering code	Flash (KB)	Package	Package type	Temperature operating range
GD32E103T8U6	64	QFN36	Green	Industrial -40 °C to +85 °C
GD32E103TBU6	128	QFN36	Green	Industrial -40 °C to +85 °C
GD32E103C8T6	64	LQFP48	Green	Industrial -40 °C to +85 °C
GD32E103CBT6	128	LQFP48	Green	Industrial -40 °C to +85 °C
GD32E103R8T6	64	LQFP64	Green	Industrial -40 °C to +85 °C



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Ordering code	Flash (KB)	Package	Package type	Temperature operating range
GD32E103RBT6	128	LQFP64	Green	Industrial -40 °C to +85 °C
GD32E103V8T6	64	LQFP100	Green	Industrial -40 °C to +85 °C
GD32E103VBT6	128	LQFP100	Green	Industrial -40 °C to +85 °C



7. Revision history

Table 7-1. Revision history

Revision No.	Description	Date
1.0	Initial Release	Dec. 26, 2017
1.1	Modify section 2.6 Pin definitions	Oct. 29, 2018
1.2	Repair history accumulation error	Dec. 12, 2018
1.3	Modify section <u>5.1</u> LQFP package outline dimensions	Apr. 22, 2019
1.4	Modify section 2.6 Pin definitions	Jun. 26, 2019
1.5	Remove redundant pin function in LQFP48 and QFN36 package. Add functional description of PD0 and PD1 to the packages below 100pin. Update electrical characteristics.	Mar. 6, 2020



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